

Experiments on pinning modes in quantum Hall systems

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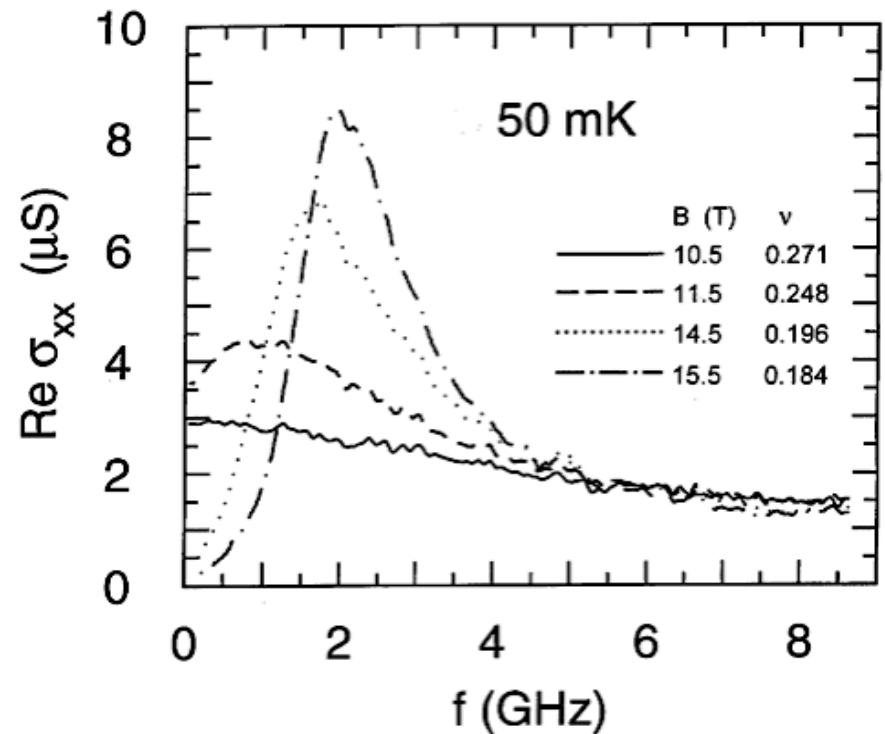
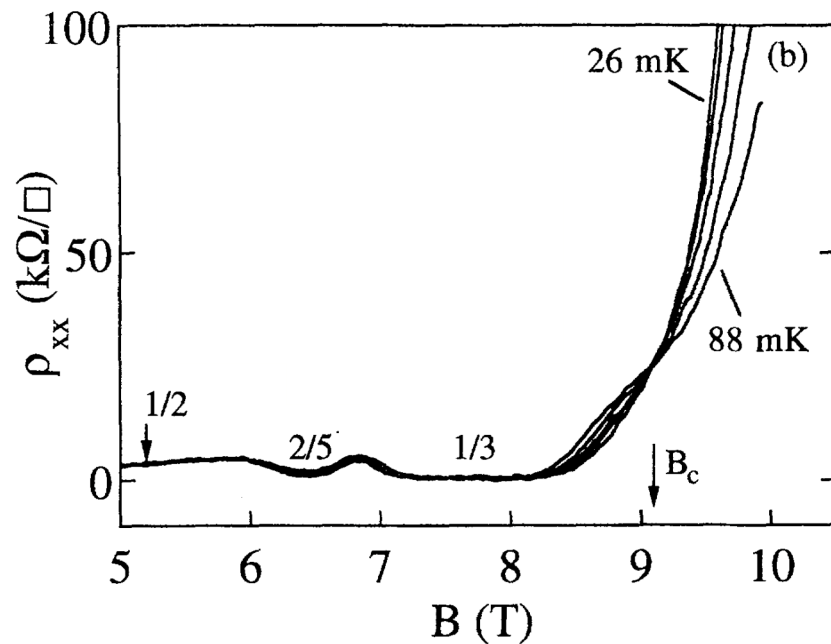
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Phenomenon of 2DES in high B :
 Insulating phase accompanied by microwave resonance



One example: insulator at termination of FQH series

Other examples to be presented...

Broadband microwave spectroscopy works where dc transport is problematic, resonance makes it a powerful tool for study of insulators

High B ground state: Wigner crystal

- Low B : Coulomb energy – kinetic energy

$$E_C - E_F$$

- High B : Kinetic energy frozen out
Landau level filling $\nu < 1/7$ to $1/6$
(high enough n)

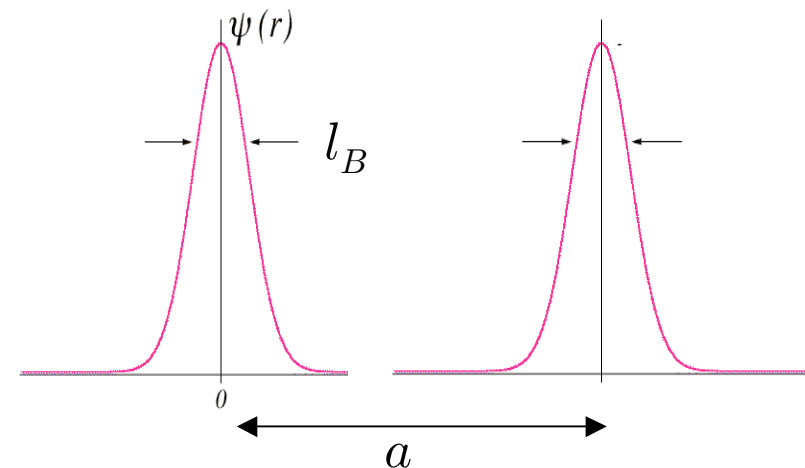
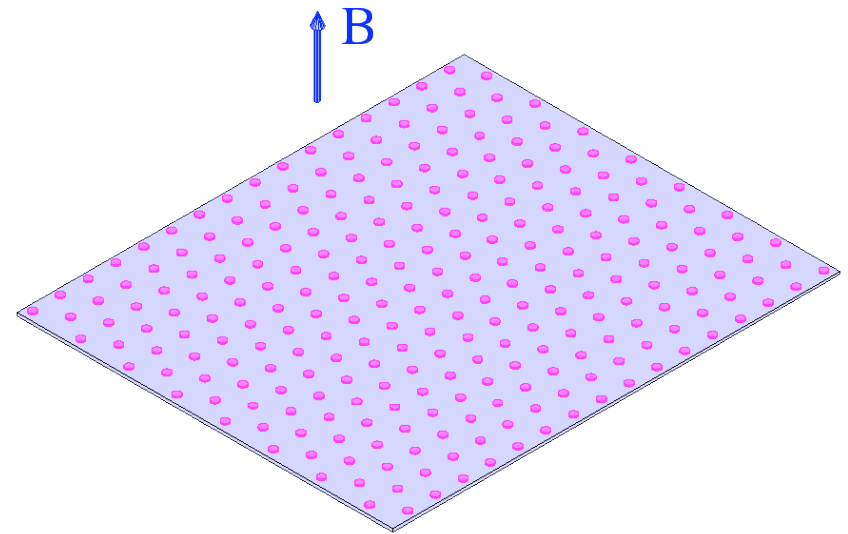
Lam and Girvin; Levesque, Weis, MacDonald '84,
Lozovik and Yudson '75; Yang and Rezayi, '02

l_B : size of electron wavefunction in
lowest Landau level

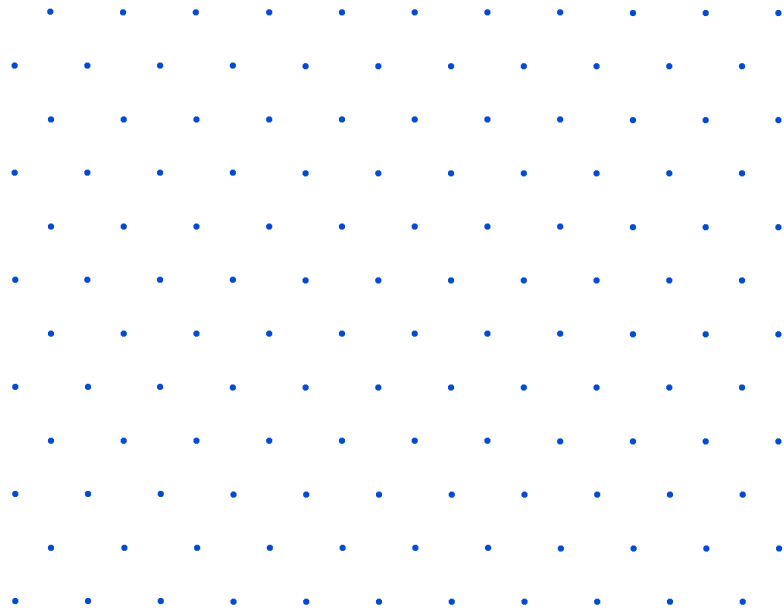
a : crystal lattice constant

$$\nu = nh/eB = (l_B/a)^2 (4\pi/3)^{1/2}$$

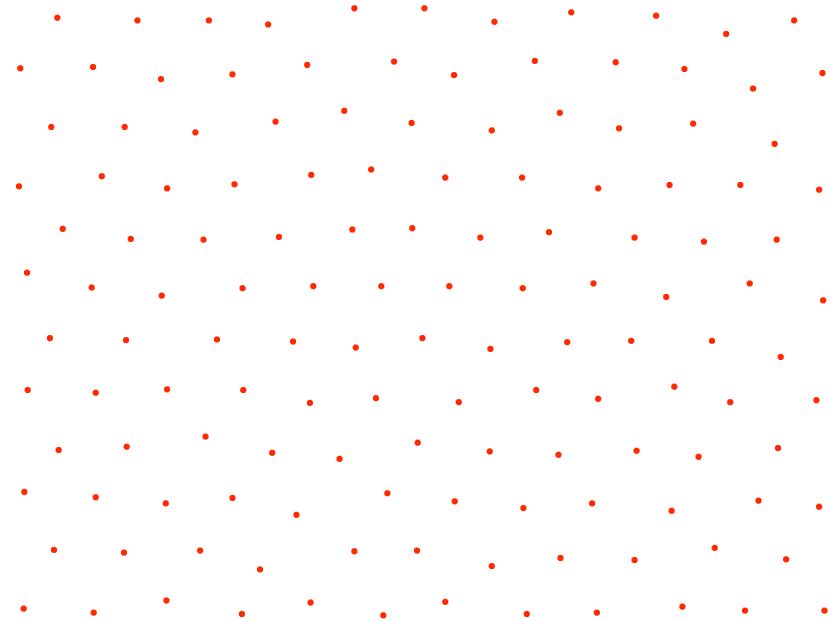
$$l_B = (\hbar/eB)^{1/2}$$



Disorder pins Wigner crystal, makes insulator



disorder off



(small) disorder on

Equilibrium positions minimizes total energy:

(electron-electron, stiffness) + (electron-disorder, pinning)

Disorder results in finite **correlation length of crystalline order, L**

Disorder: Impurities, interface roughness, donor potential

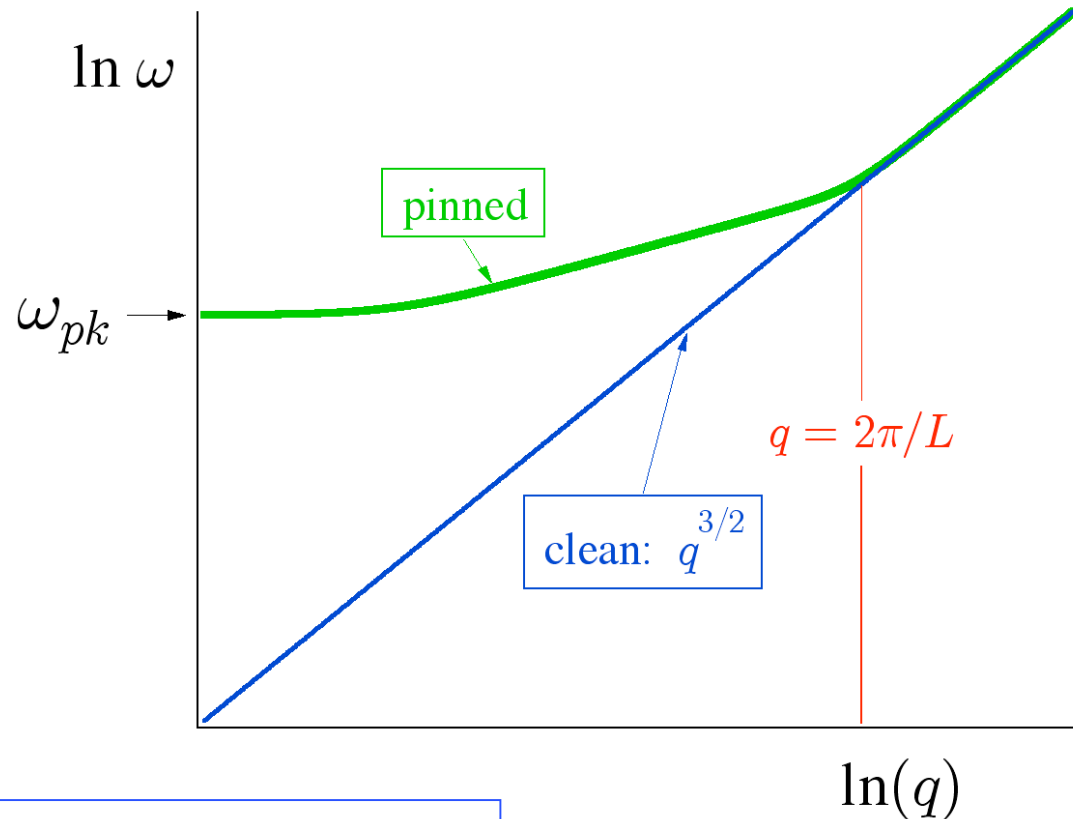
Resonance: pinning mode interpretation

Disorder induces “Pinning” Mode: small oscillation about pinned positions

Disorder

$$\Rightarrow L$$

$$\Rightarrow \omega_{pk} \sim \omega(q \sim 2\pi/L)$$

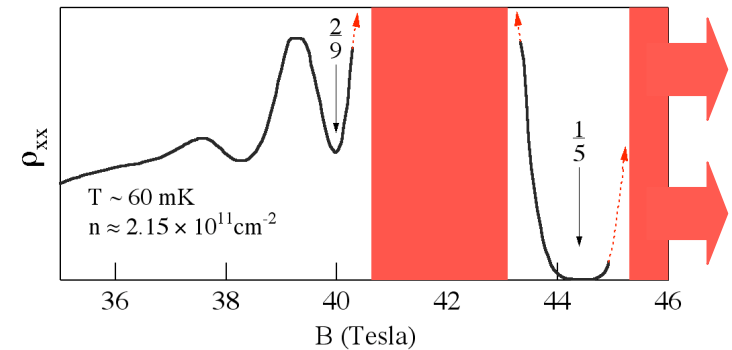
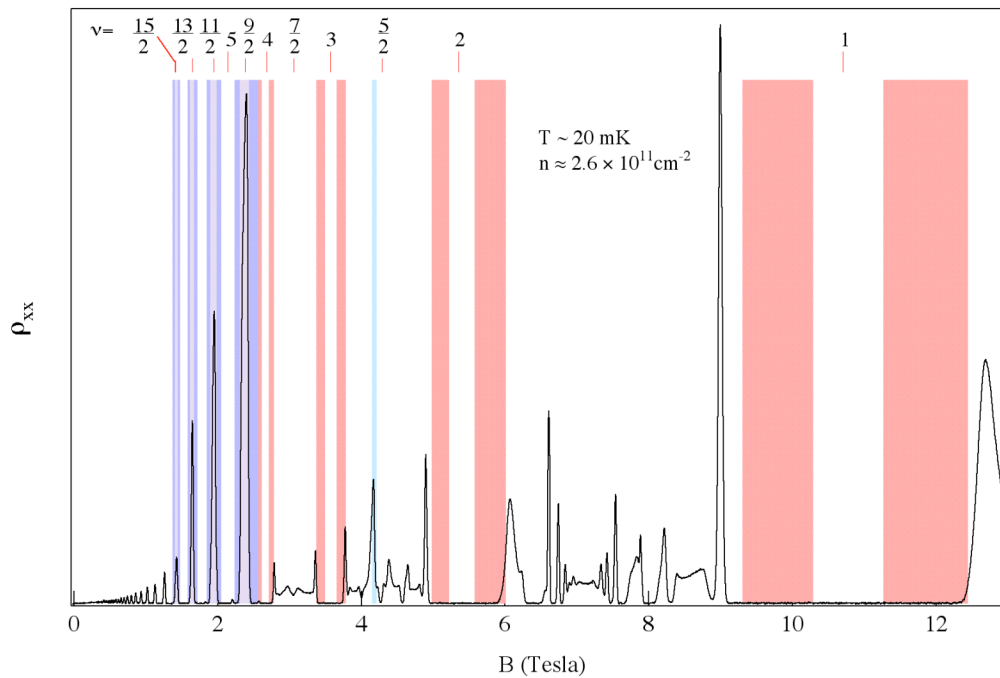


Classical Wigner crystal in high B:

Without disorder: $\omega \sim q^{3/2} B$

With disorder: saturates at low $q \sim 2\pi/L$

ν ranges of electron solids



█ Integer Quantum Hall Effect Wigner Crystal

█ High B Wigner Crystal

█ Bubble phase

█ Stripe phase (anisotropic)

█ N=1 Landau level bubble phase

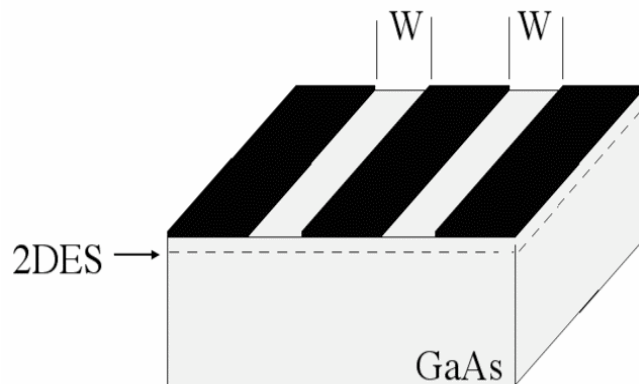
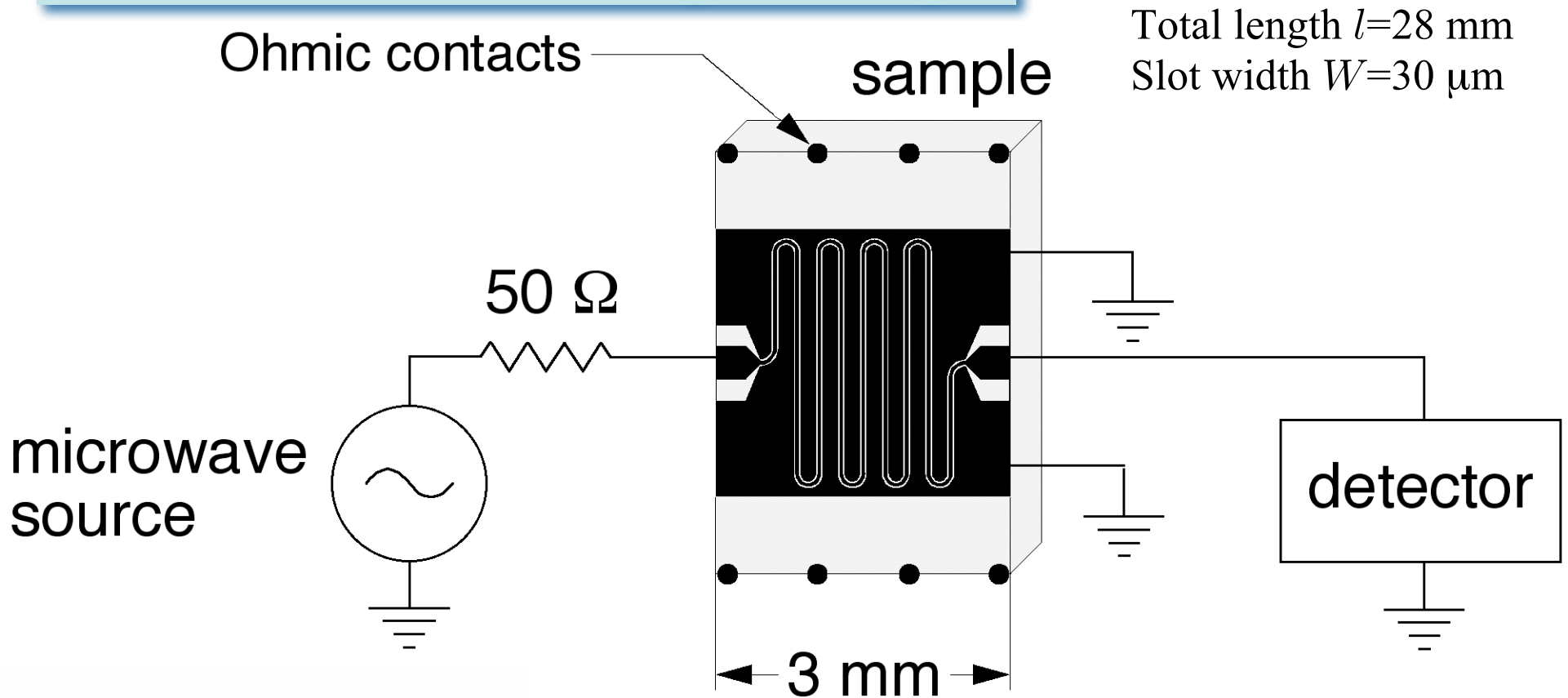
Outline

- Microwave measuring technique
- pinning mode “basics”
 - Sample (confinement) dependence
 - Evidence of collective localization
 - Oscillator model and sum rule
 - f_{pk} vs n, B
 - Correlation lengths of crystalline order

Examples of “applications”:

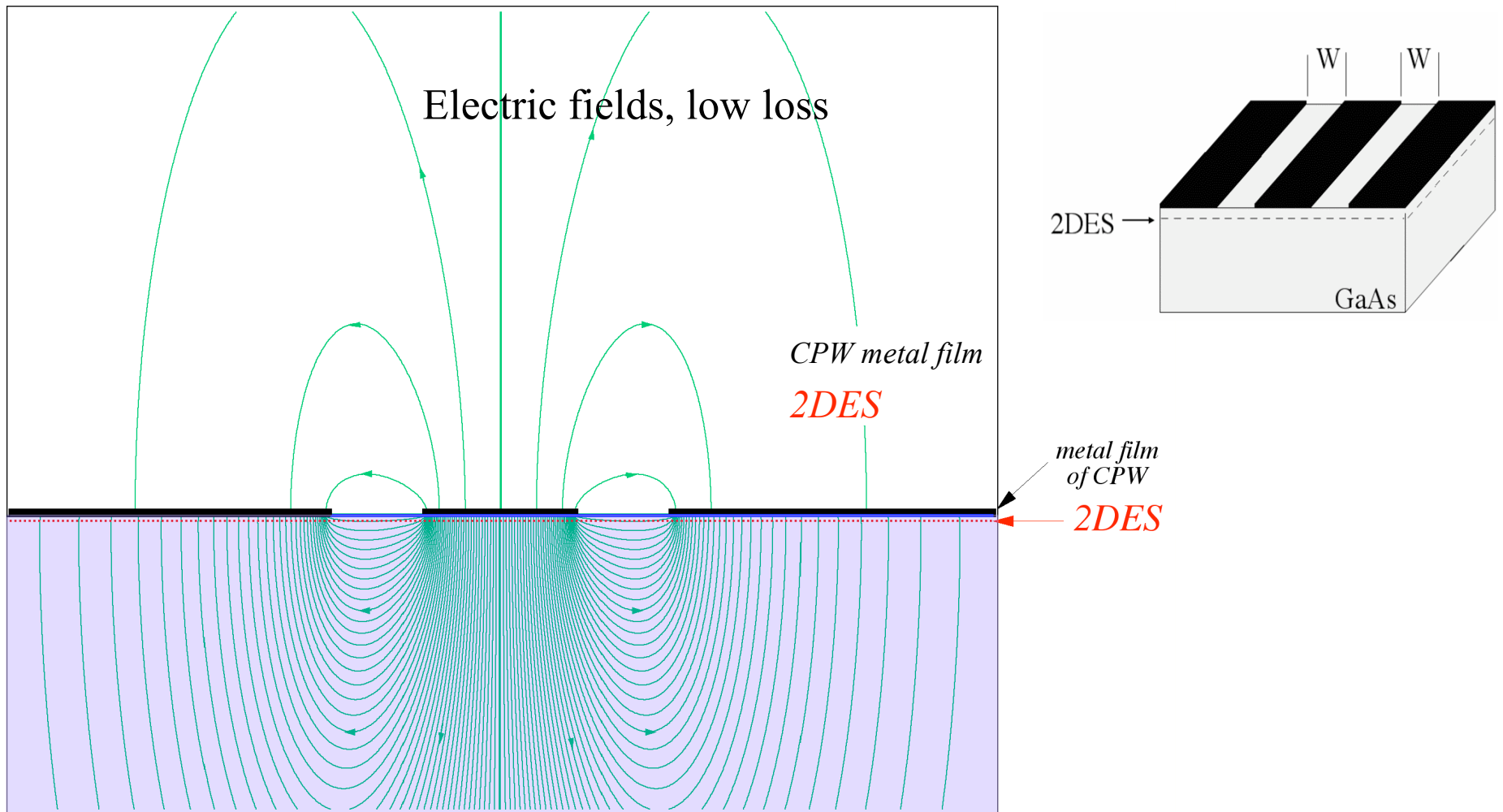
- resonance in IQHE plateau regions:
 - Wigner crystallization in IQHE + skyrmion effects
- bilayers: evolution with effective separation d/a
 - Evidence for interlayer correlation

Microwave measuring technique



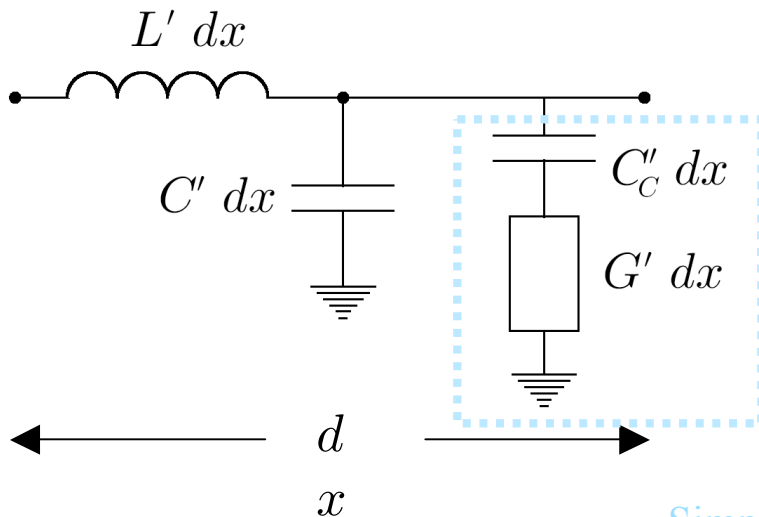
- Metal film makes coplanar waveguide (CPW) transmission line
- Center conductor driven, side planes grounded “like coax”
- $\text{Re}(\sigma_{xx})$ from 2DES effect on signal

Microwave measurement, Electric fields



- Relevant 2DES is under the slots
- CPW - 2DES coupling is capacitive

Re(σ_{xx}) from transmitted power: Circuit model



$$G' = 2\sigma_{xx}/W$$

$$\omega C'_C \gg C'$$

$$Z_0 = \sqrt{\frac{L'}{C'}} = 50 \Omega$$

Characteristic impedance

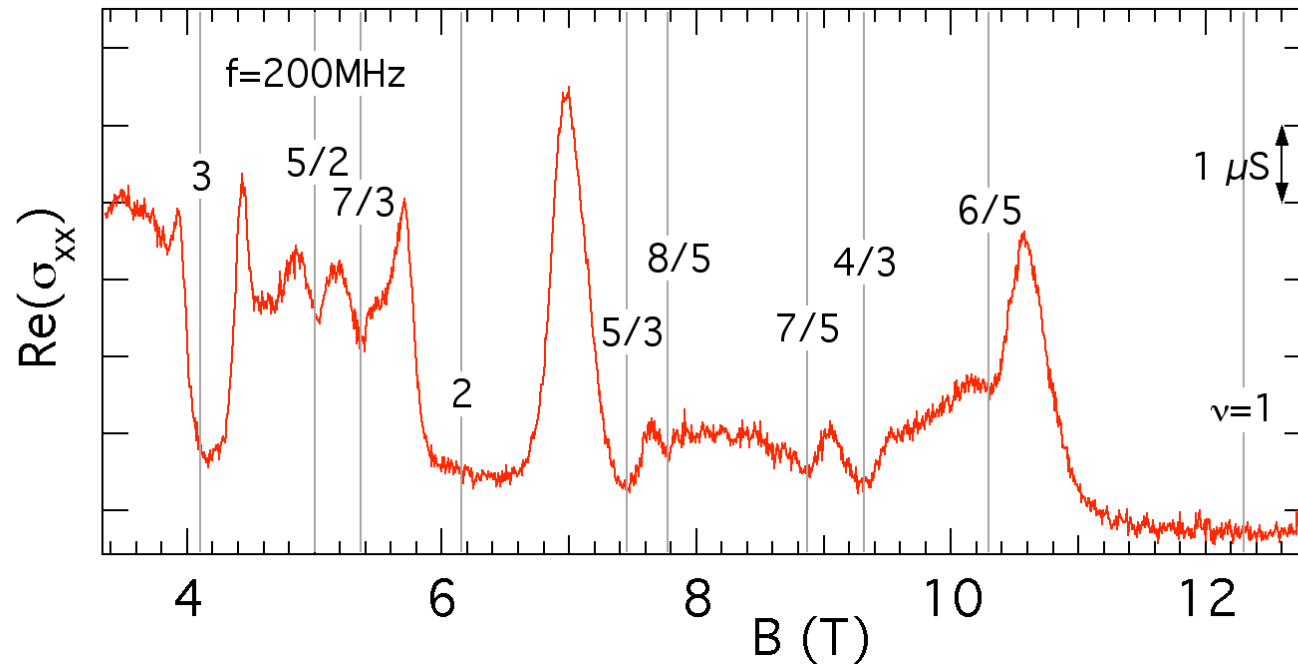
Simplified 2DES and coupling

Relative transmitted power (in low loss limit, $|\sigma_{xx}| \ll \omega C'W$):

$$P = \exp(-lZ_0 \text{Re } \sigma_{xx}/2W)$$

- f -independent extinction (l is length along line)
- Corrections are considered for reflections, larger loss, distributed capacitive coupling
- Assumes no q -dependence of σ_{xx} accessed by transmission line

Quantum Hall effect: finite frequency transport

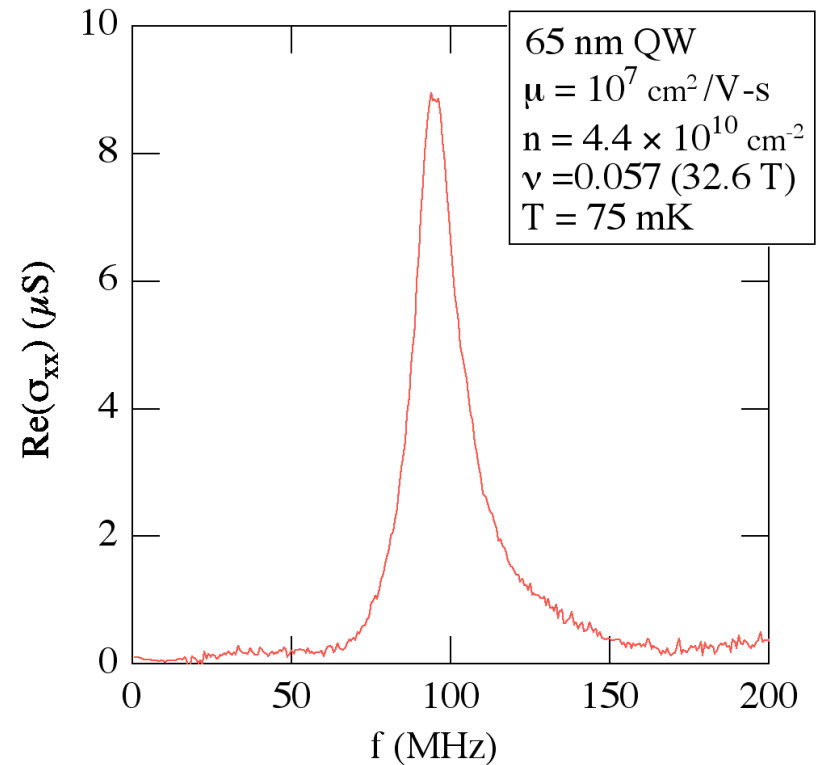
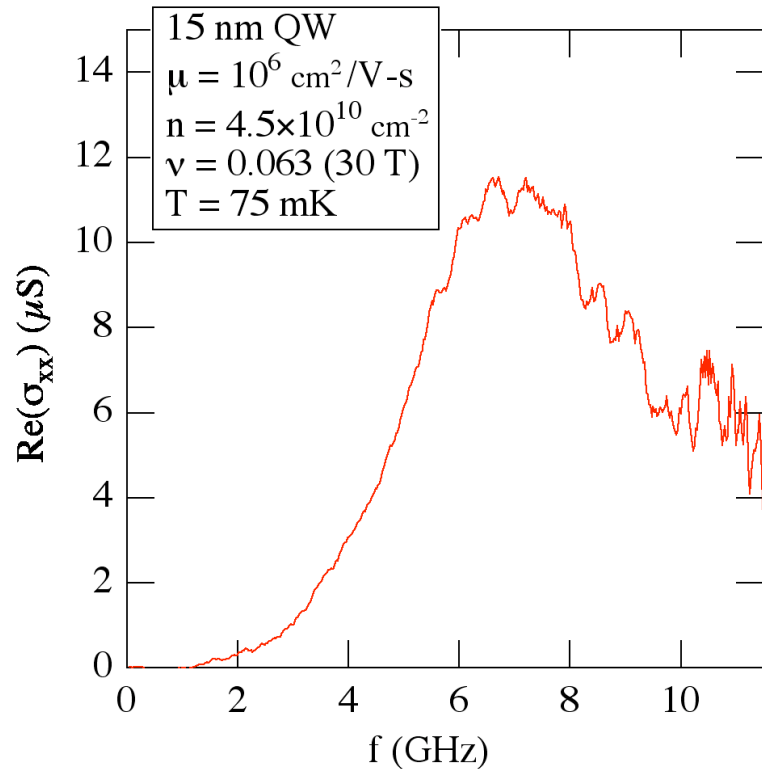


Data presented as $\text{Re}(\sigma_{xx})$

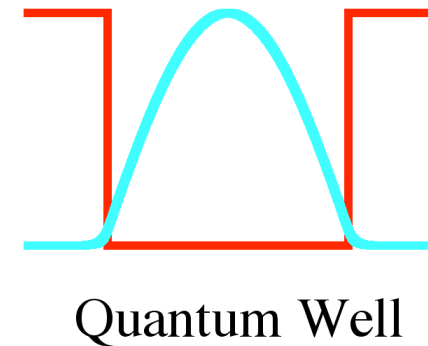
$$\sigma_{xx} = \rho_{yy} / (\rho_{xx} \rho_{yy} + \rho_{xy}^2)$$

low wavevector (q) limit (most of talk)

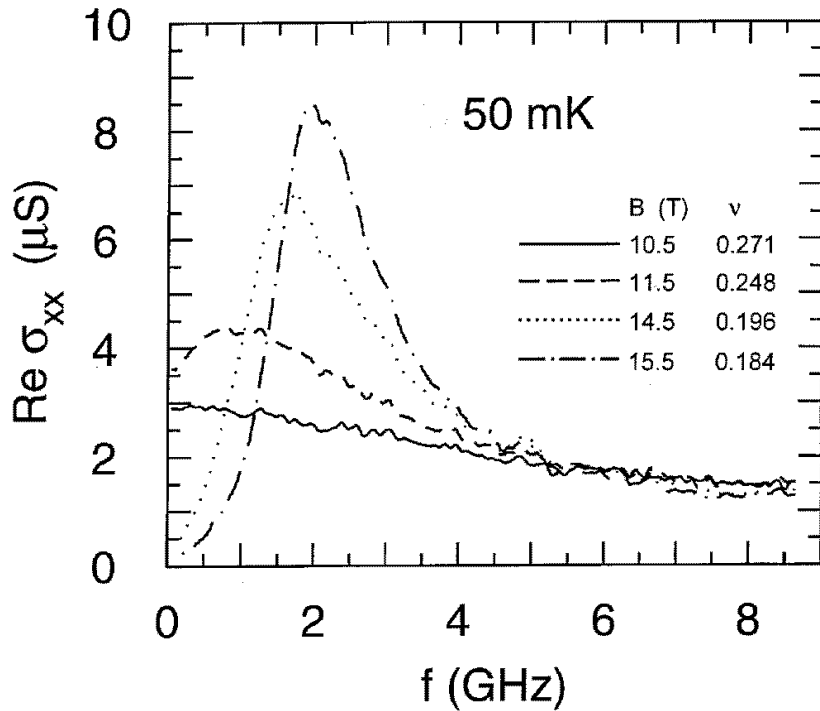
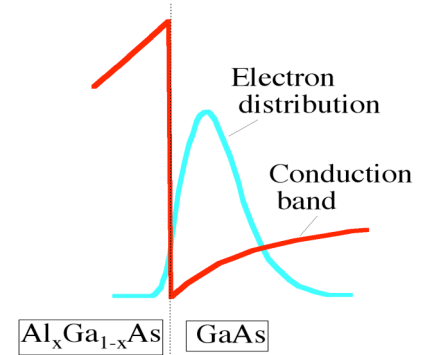
f_{pk} is larger for larger disorder: Quantum Wells



- Enormous range of f_{pk}
- Interface roughness (Fertig '99) as relevant disorder (vs impurities, remote ionized donor potential):
- Wide QW
⇒ Reduced influence of interfaces on confinement
⇒ reduced disorder



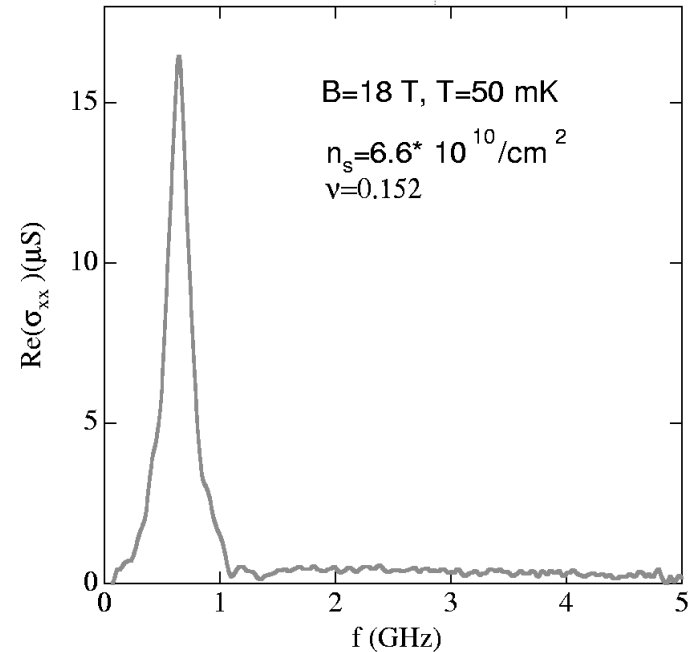
f_{pk} is larger for larger disorder: heterojunctions



$$n \approx 6.9 \times 10^{10} \text{ cm}^{-2}$$

$$\mu \approx 5.0 \times 10^5 \text{ cm}^2/\text{Vs}$$

$$f_{pk} \approx 2 \text{ GHz, at } 15.5 \text{ T}$$



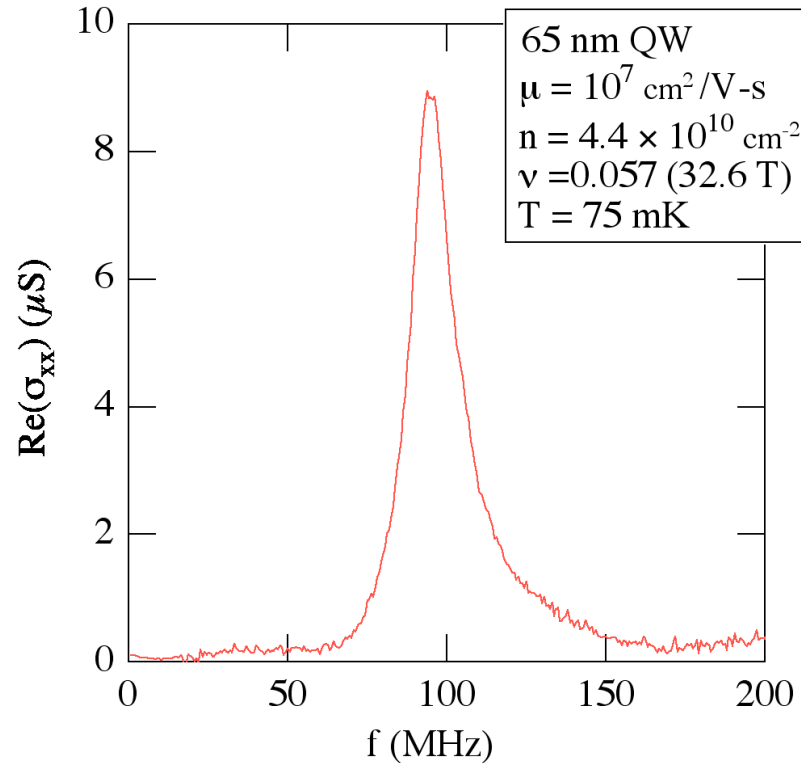
$$n \approx 6.6 \times 10^{10} \text{ cm}^{-2}$$

$$\mu \approx 5.0 \times 10^6 \text{ cm}^2/\text{Vs}$$

$$f_{pk} \approx 0.6 \text{ GHz}$$

(sample 1)

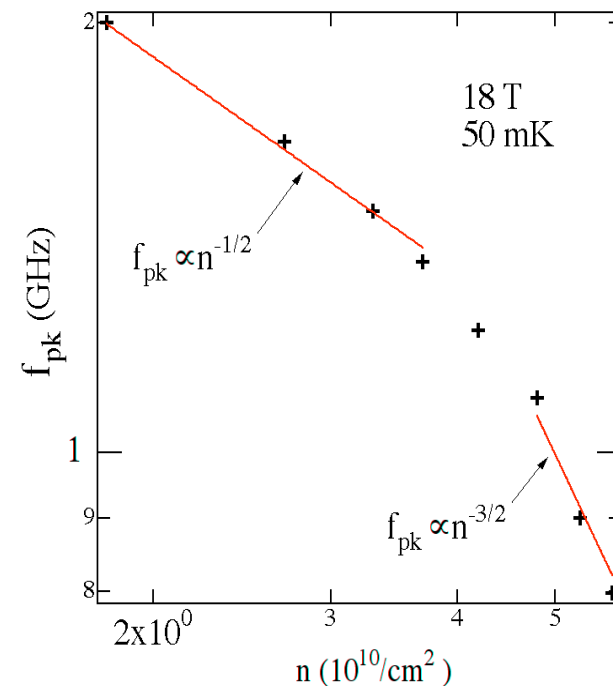
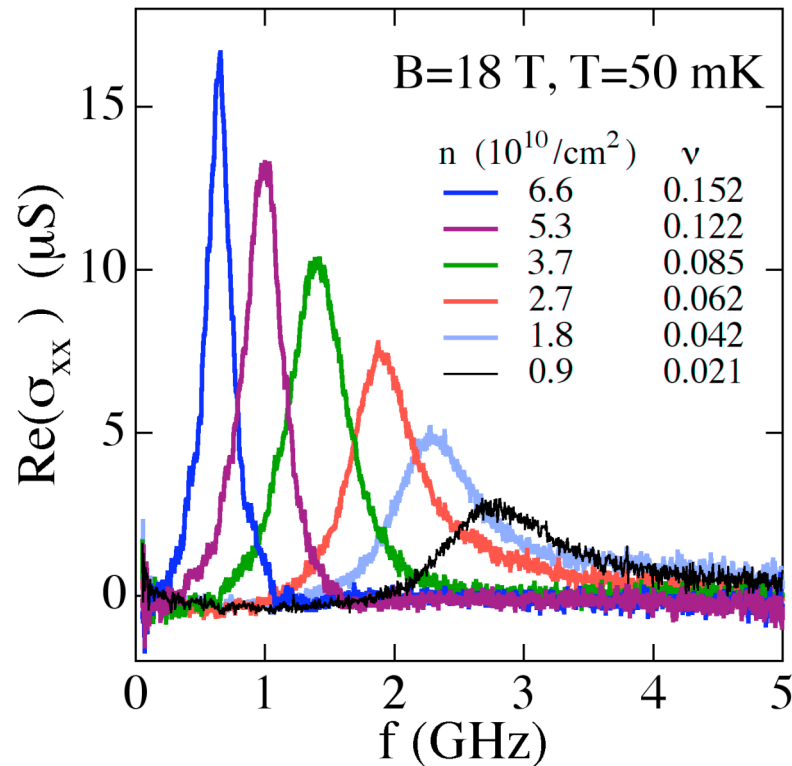
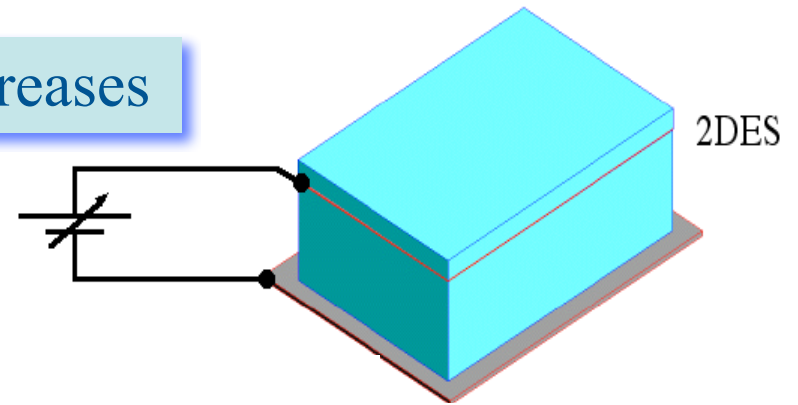
Correlated Electron Solid



- Lowest f_{pk} and Δf 95 MHz 10 MHz
 4.5 mK 0.5 mK
- $hf_{pk}/k_B \ll T \Rightarrow$ pinning, collective localization, electron solid
- Rules out individual electrons in traps
- General for cleaner samples at higher n , includes other insulators

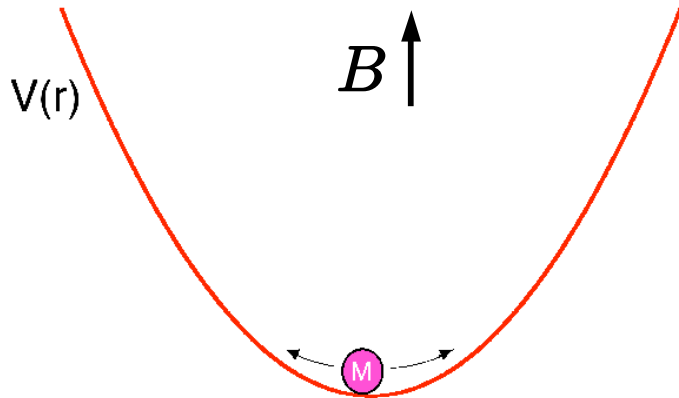
Decrease *density* with backgate: f_{pk} increases

Single layer 2DES sample



- Weak pinning: minimize (impurity + deformation) energy $\Rightarrow L$
- Reducing $n \Rightarrow$ weaker carrier-carrier interaction
- \Rightarrow Carriers “fall further into impurity potential”
- \Rightarrow Average pinning, so f_{pk} increases

Harmonic oscillator model of pinning mode



Charge in “pinning” potential

$$V(x, y) = \frac{M\omega_0^2(x^2 + y^2)}{2}$$

“pinning” frequency ω_0 ,
cyclotron frequency $\omega_c = eB/m^*$

Two modes: $\omega_+ \geq \omega_c$

$\omega_- = \omega_0^2/\omega_c$ (for $\omega_0 \ll \omega_c$)
➔ Microwave resonance

Observed resonance frequency: $f_{pk} = \omega_0^2/2\pi\omega_c$

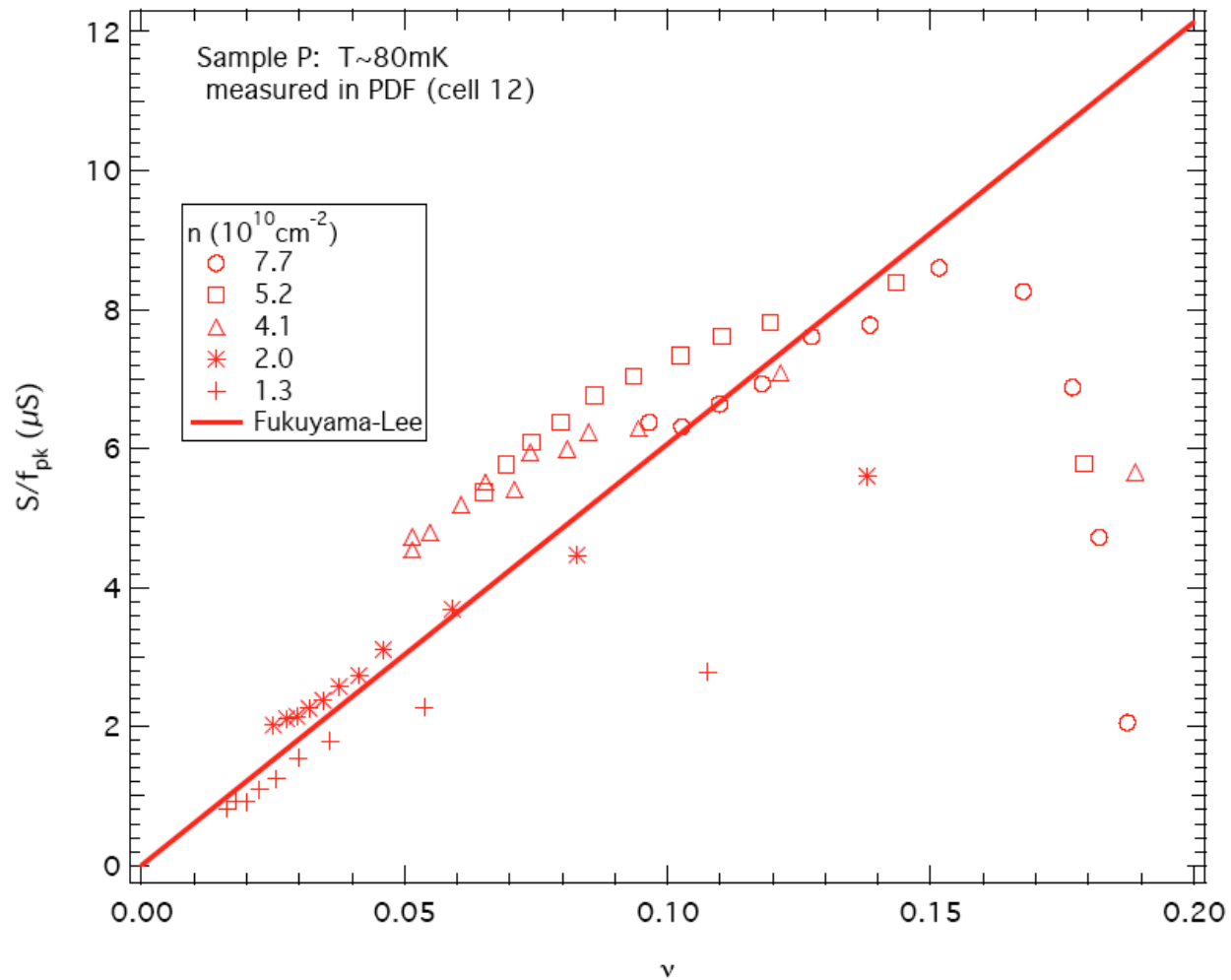
ω_- sum rule: $S_- = \int_0^\infty \text{Re}[\sigma_{xx}(f)]df = \frac{n_s^* e \pi f_{pk}}{2B}$

$$\frac{S_-}{f_{pk}} = \frac{n_s^* e \pi}{2B}$$

n_s^* : participating carrier density

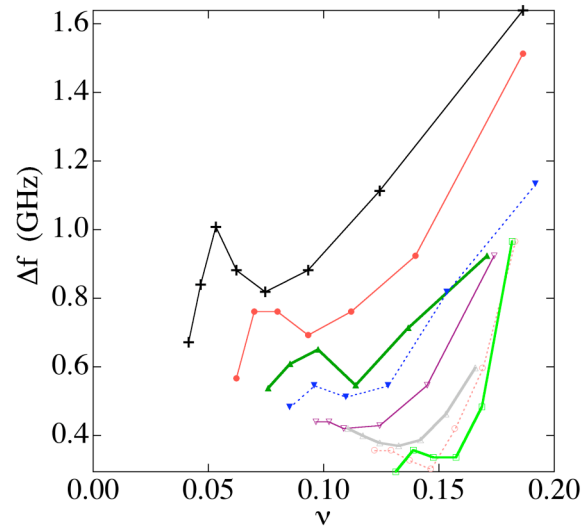
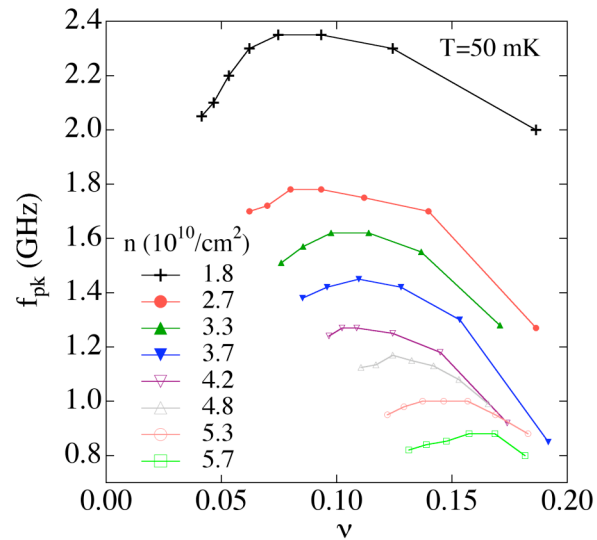
$$S_- \propto \frac{\omega_0^2}{\omega_c^2} \quad (S_- \ll S_+)$$

S/f_{pk} vs ν : linear, slope close to oscillator model value



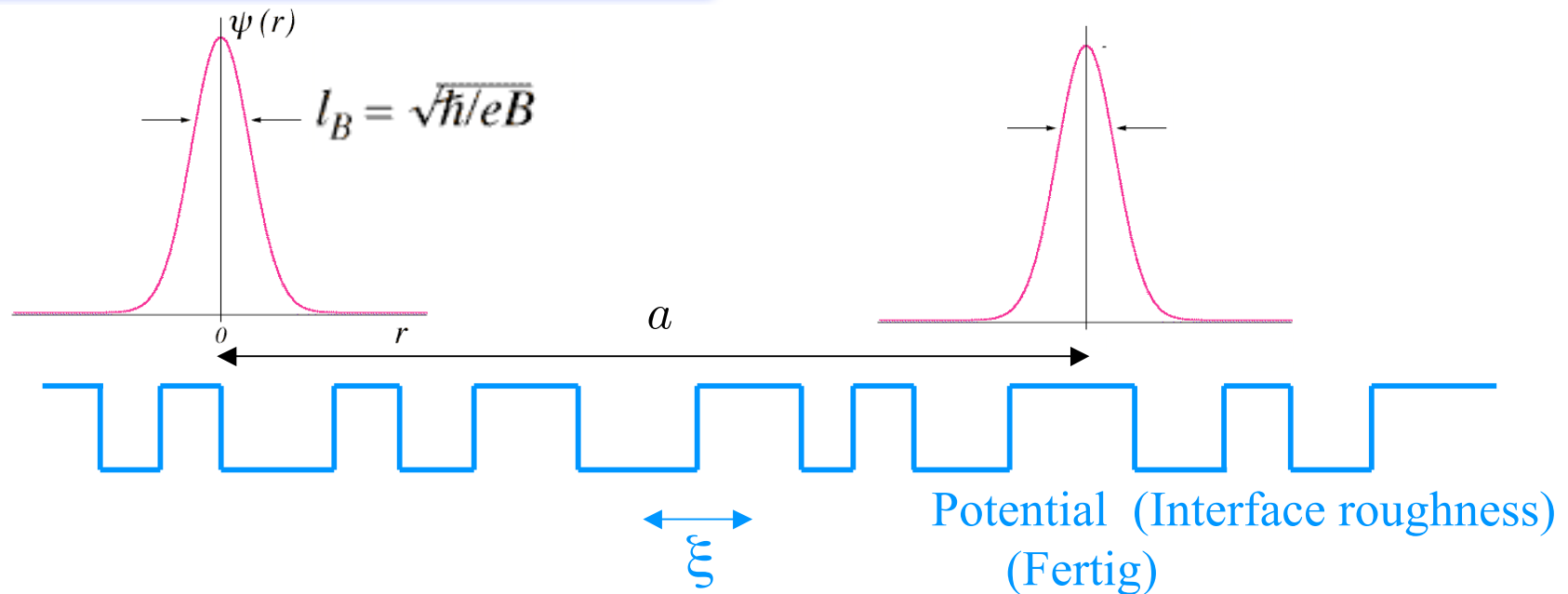
Full participation: not isolated traps

$f_{pk}, \Delta f$ vs ν



- Maxima in f_{pk} vs ν
- Oscillator model: $f_{pk} \propto \nu$ (for fixed n)--not achieved
- Existing theories for weak pinning limit, based on interplay of l_B and disorder lengths:
 - $f_{pk} \propto 1/\nu$ (Fertig '99)
 - or $1/\nu^2$ (Chitra'98, Fogler & Huse '01)
- Δf : complicated...

B dependence of f_{pk} , discussion



l_B : size of electron wavefunction in lowest Landau level

a : lattice constant

ξ : disorder correlation length(s)

B dependence of f_{pk} from electron-impurity interaction:
interplay between l_B and ξ

How can a pinning mode be so sharp?

domain size (coherence length) L

Possibilities:

1. Dilute identical impurities as oscillators:
but oscillator strength too large
2. Motion coherent over large length scale
 $L_B \sim L$, averaging disorder
Due e-e interaction + high B

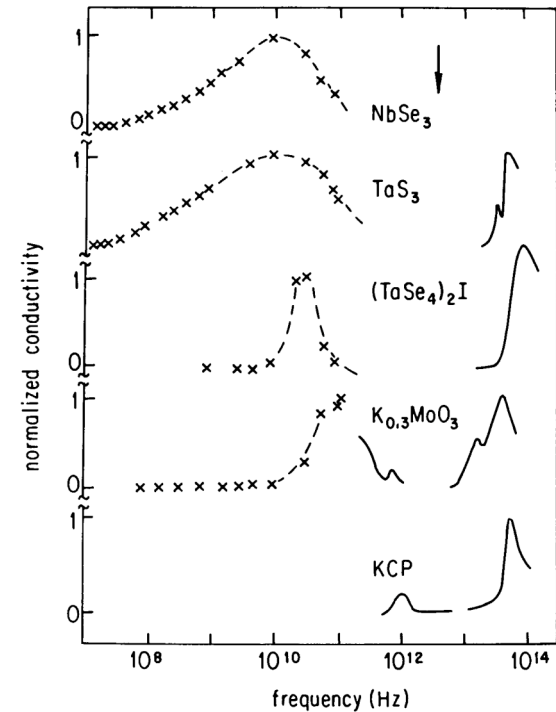


Figure 9.4. Frequency dependent conductivity measured in several compounds in their charge density wave state (Grüner, 1988). The arrow indicates the gap measured by tunneling for NbSe_3 .

Theories: Fertig, Fogler and Huse, Chitra and Giamarchi

Correlation lengths of Wigner crystalline order (from f_{pk})

L is *Larkin* length over which (deviations from lattice) \sim (disorder correlation length ξ)
 or (deformation energy) \sim (pinning energy)

L_a is length over which (deviations from lattice) \sim (lattice constant a)

For interface roughness, $\xi \ll a$

$L_a/L \sim (a/\xi)^\beta$, $\beta \sim 3$ (Fogler and Huse, '00)

Find L from

f_{pk} and elastic properties of classical WC:

$$\mu_{t,cl} = \frac{0.245e^2 n^{3/2}}{4\pi\epsilon_0\epsilon}; \quad \epsilon = 12.8$$

$$\omega_0 = \sqrt{2\pi f_{pk}\omega_c}$$

$$c_t = (\mu_t/nm^*)^{1/2}, \text{ where } c_t \text{ is } B=0 \text{ transverse phonon}$$

$$= \frac{2\pi c_t}{L}$$

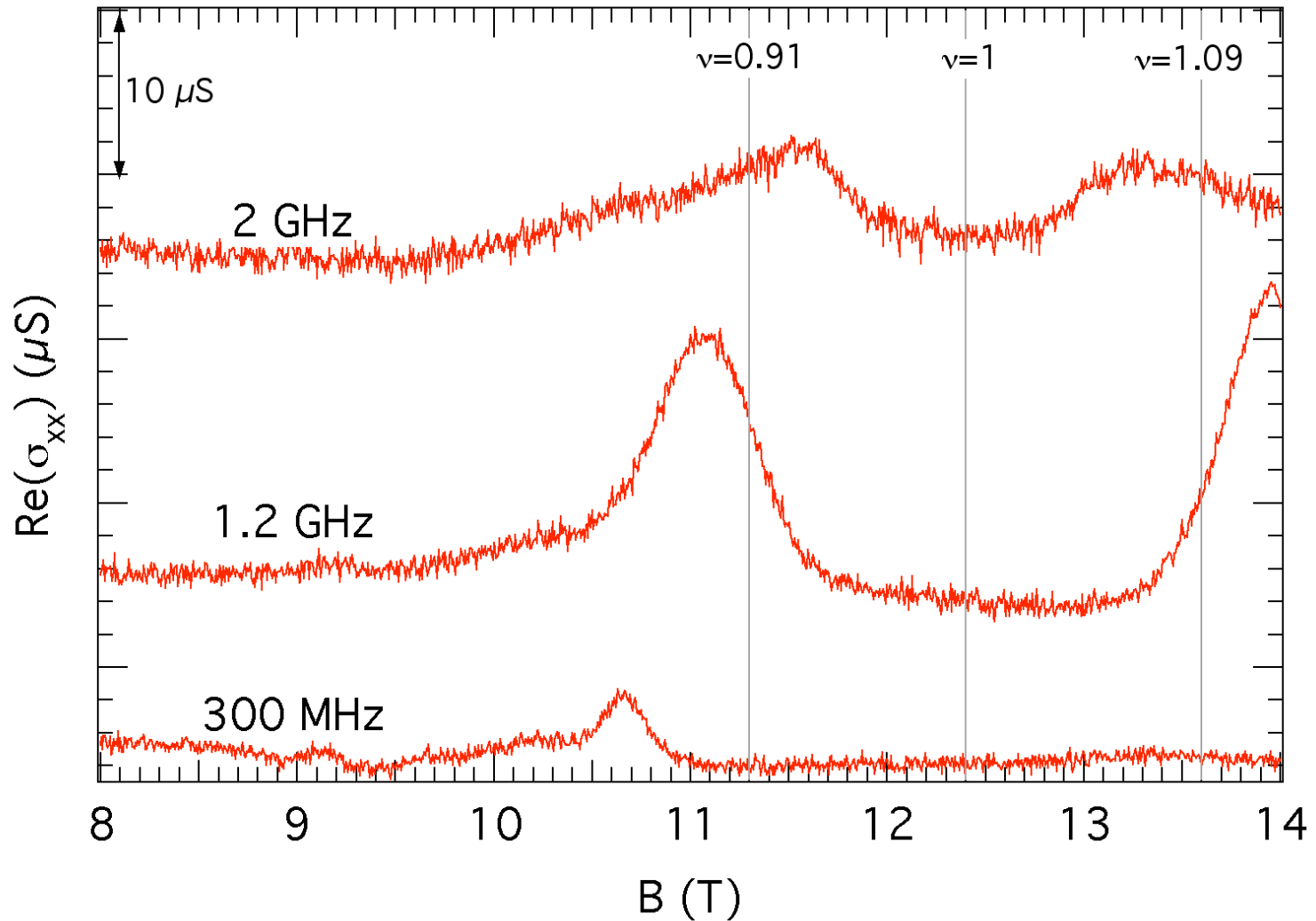
$\mu_{t,cl}$ is shear modulus (Bonsall and Maradudin '77)

$$L = \left(\frac{2\pi\mu_{t,cl}}{nm^* f_{pk}\omega_c} \right)^{1/2} = \left(\frac{2\pi\mu_{t,cl}}{neB f_{pk}} \right)^{1/2}$$

	f_{pk}	L/a
For $n \approx 4.5 \times 10^{10} / \text{cm}^2$, $a \approx 0.051 \mu\text{m}$:	95 MHz	21
	7 GHz	2.7

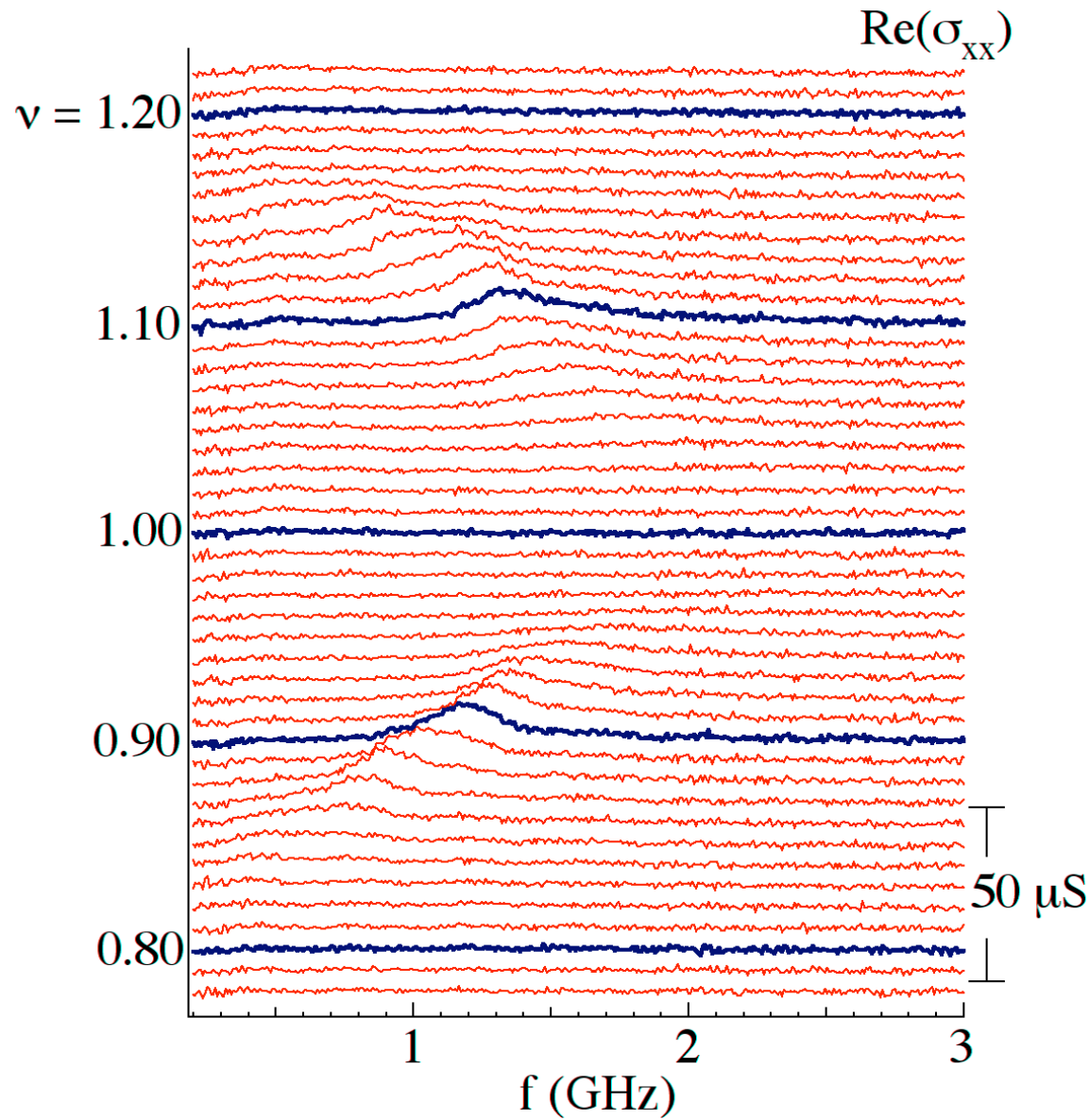
Crystal may be quite ordered, $L_a \gg a$, even when $L \sim a$

Higher ν : evidence for Wigner crystallization in IQHE



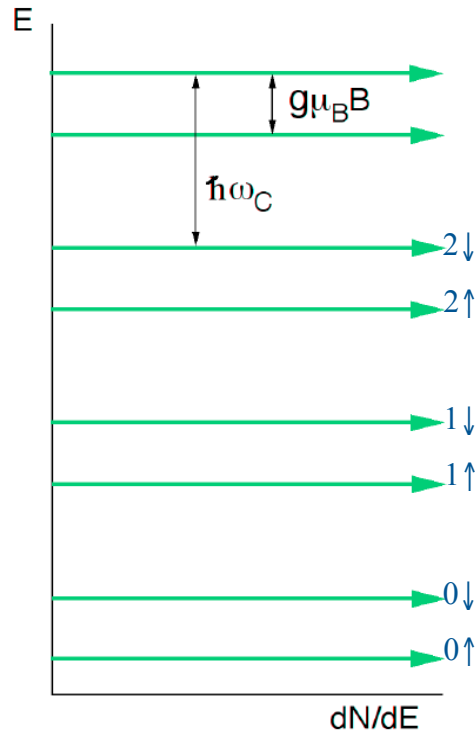
Narrowing of IQHE minimum with f , $\text{Re}[\sigma_{xx}(f)]$ not monotonic

Resonances on either side of $\nu=1$, vanishing just on $\nu=1$

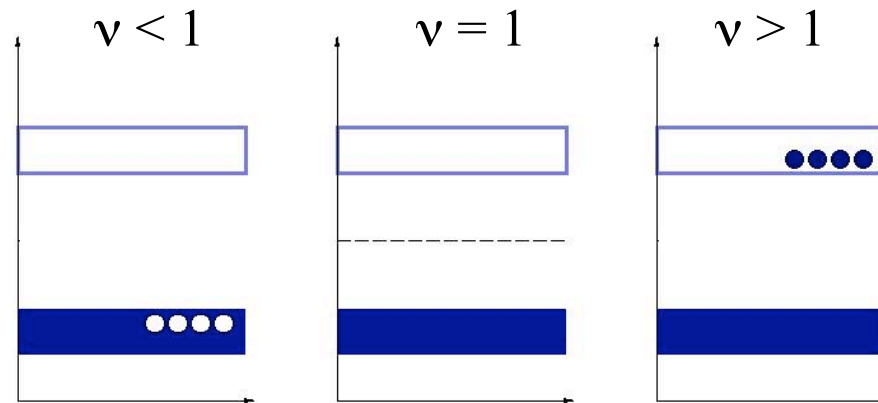


f_{pk} increases as $\nu \rightarrow 1$

Interpretation: “Integer Quantum Hall Wigner Crystal” (IQHWC)



... made up of top Landau level (LL) electrons or holes
 IQHE when (top LL contribution to dc σ_{xx}) $\rightarrow 0$



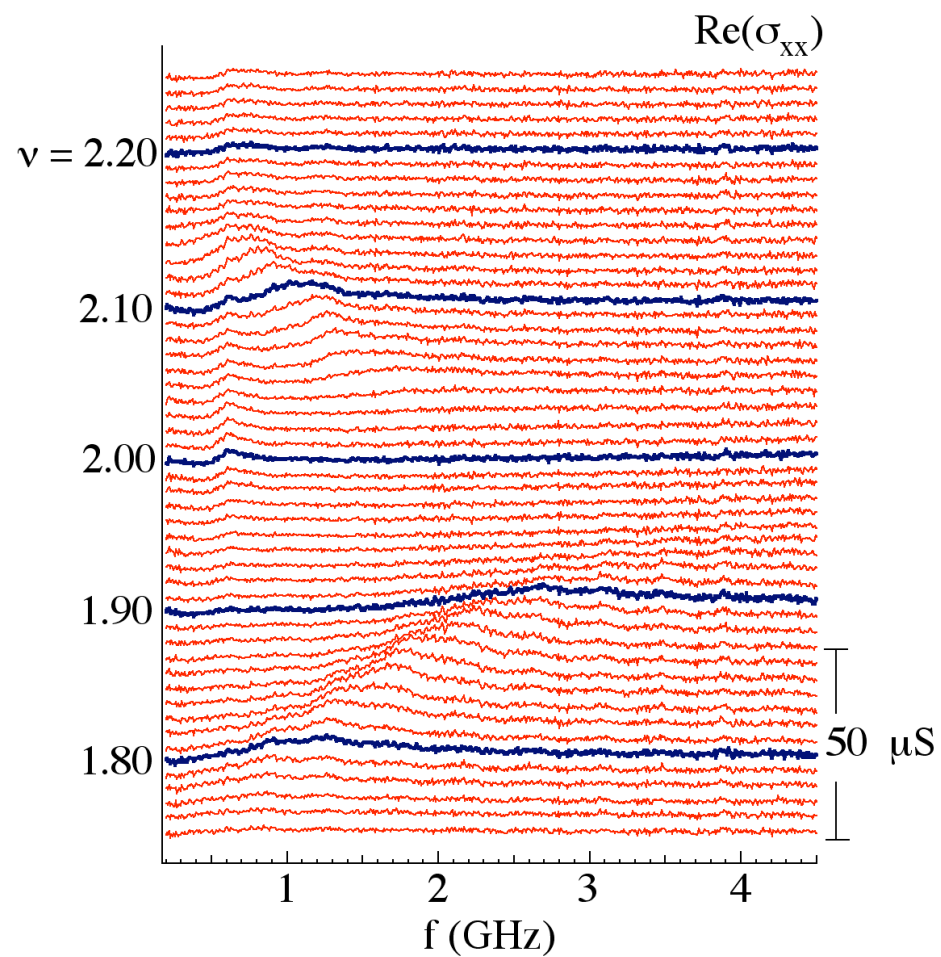
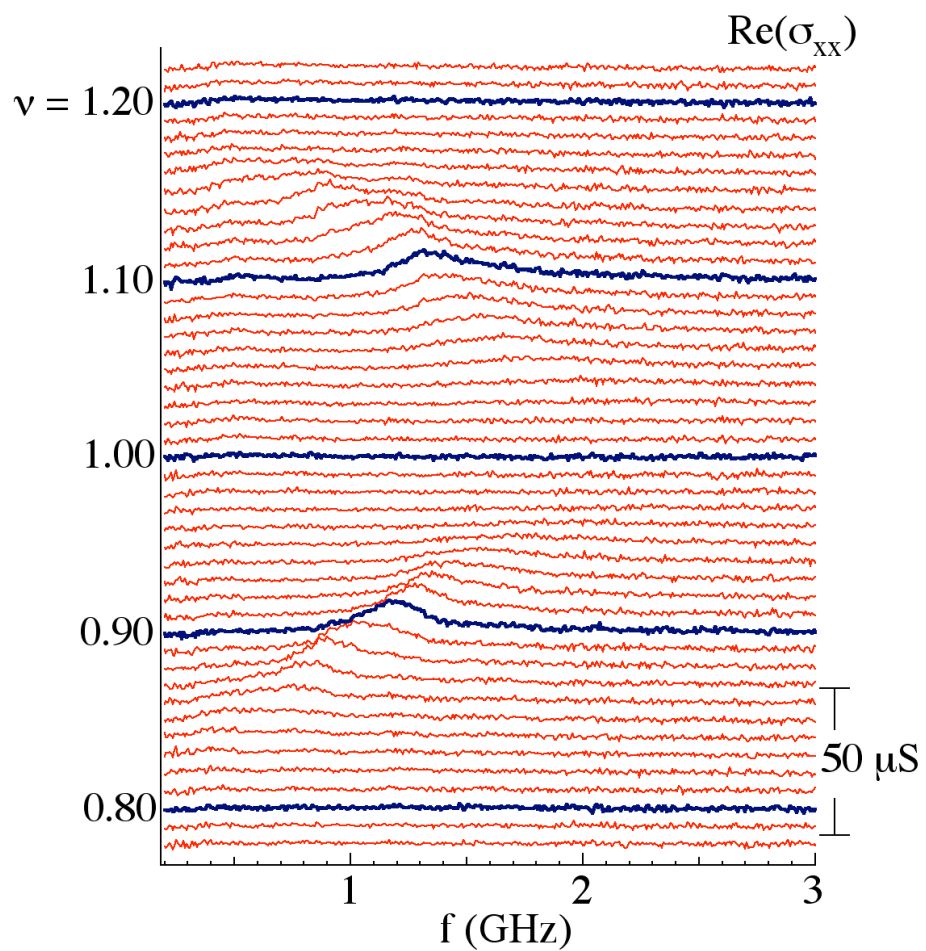
$\nu = K + \nu^*$, K an integer

Density of top LL electrons = $\pm n^* = \nu^* n / \nu - \nu^* n / K$
 holes

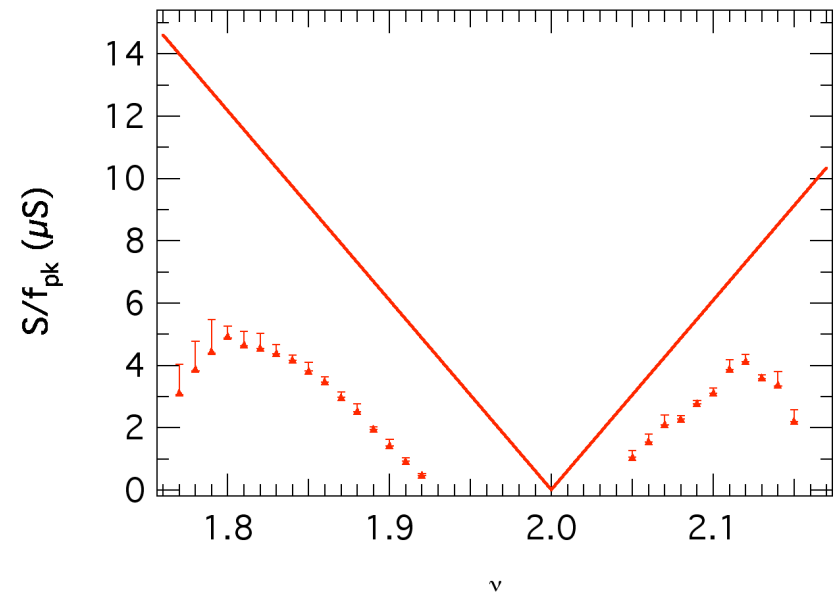
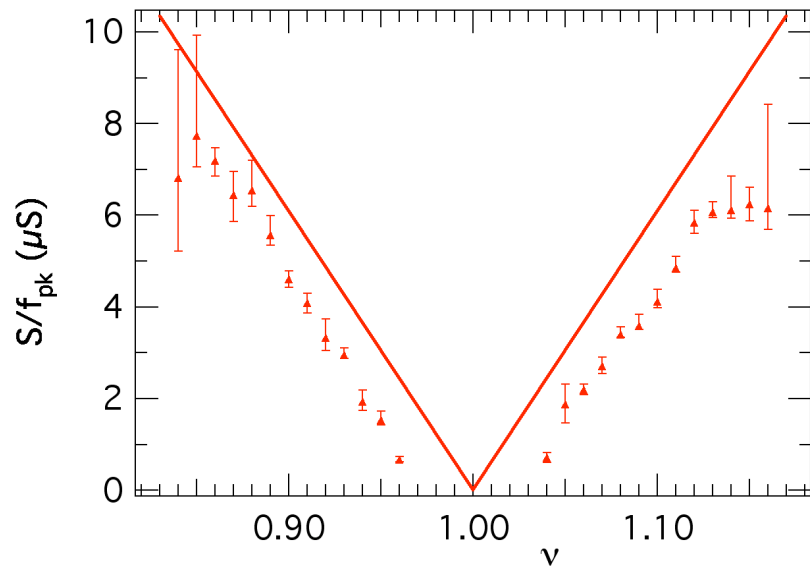
$n^* \rightarrow 0$ for exact integer ν , $T=0$

Interpret analogous to high B lowest LL except varying B varies n^*

Resonance around $\nu=1$ and $\nu=2$



“IQHE-WC” resonance oscillator strengths around $\nu=1$ and 2

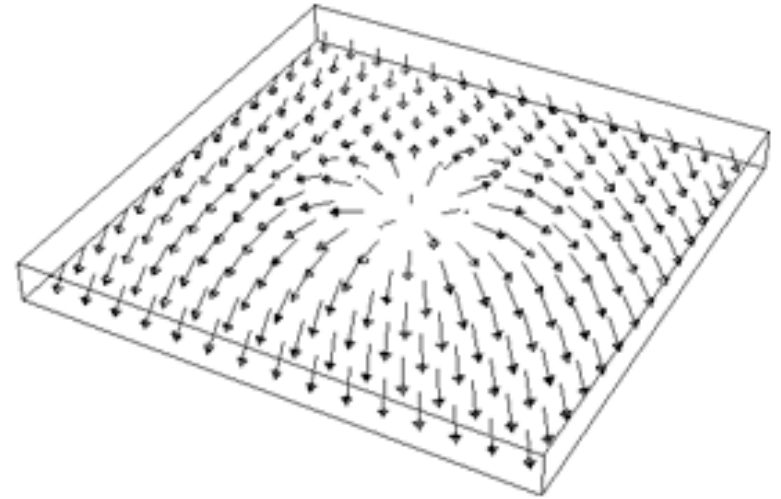


$S/f_{pk} \propto$ participating density

Skyrmions: charged excitations near $\nu = 1$

Problem:

resonances around $\nu = 1$ and 2 (and 3 and 4) are similar, but the particles near $\nu=1$ are expected to be skyrmions.



- Exchange energy gained at expense of Zeeman energy
- $\tilde{g} = E_Z/E_C = g\mu_B B / (e^2/4\pi\epsilon\epsilon_0 l_B) \approx .012$ for $n=10^{11}$ cm⁻² in perp. B
- Larger \tilde{g} decreases spin, “Size of skyrmion”, S
- S decreases to 1 for $\tilde{g} > 0.054$ (Sondhi et al 93)

Experimental evidence:

Barrett et al 95 (Knight shift); Bayot et al. 96, heat capacity

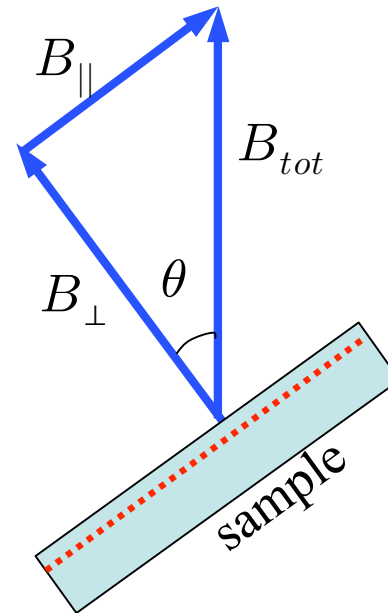
Schmeller et al 95 (T dependent transport); Aifer, Goldberg, Broido (optics)

Tilted field

For given ν , l_B (B_{\perp})
Vary Zeeman energy (B_{tot})

$$\tilde{g} = E_Z/E_C = g\mu_B B / (e^2/4\pi\epsilon\epsilon_0 l_B)$$

Also affects vertical wavefunction

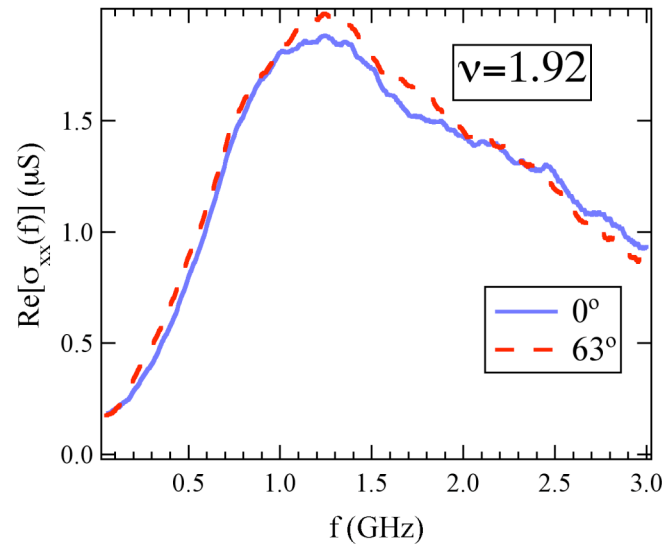
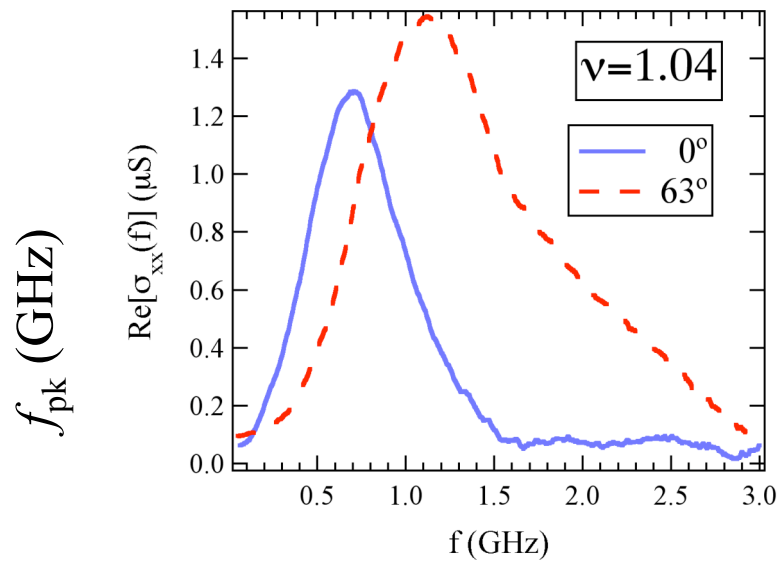


Schmeller et al 95 (T dependent transport)

Compare near $\nu = 1$ and 2

$n = 1.15 \times 10^{11} \text{ cm}^{-2}$, $\mu \sim 10^7 \text{ cm}^2/\text{Vs}$ 50nm QW
 $B = 4.6 \text{ T}$ for $\nu = 1$, $\theta = 0^\circ$

$$n^* = 0.46 \times 10^{10} \text{ cm}^{-2}$$



$$\theta = 0^\circ : \tilde{g} = 0.013$$

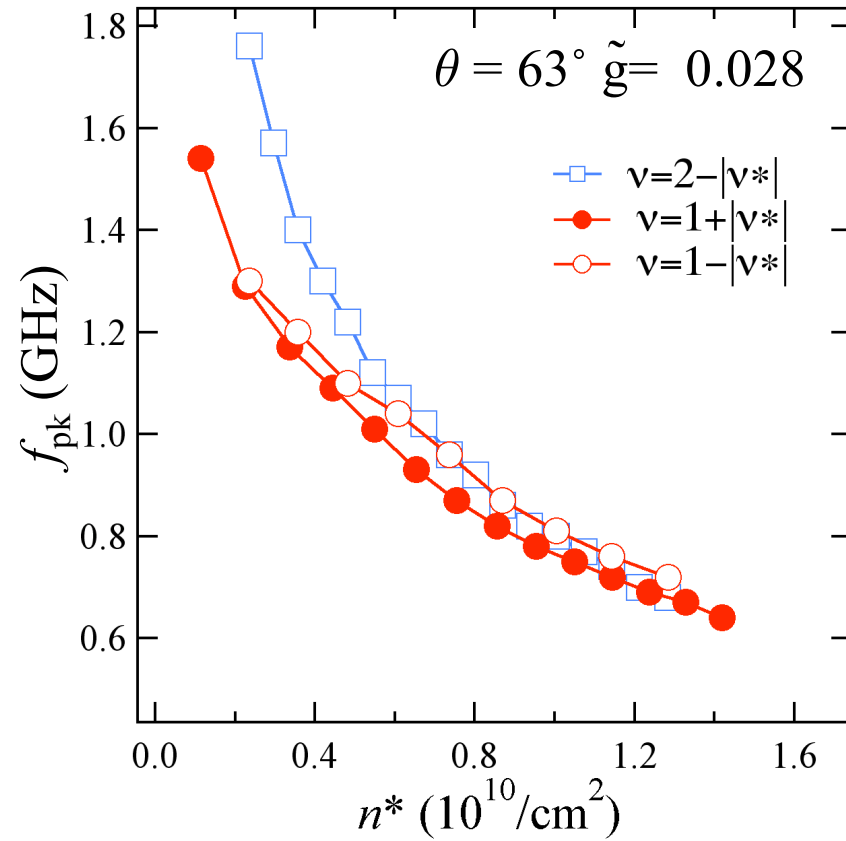
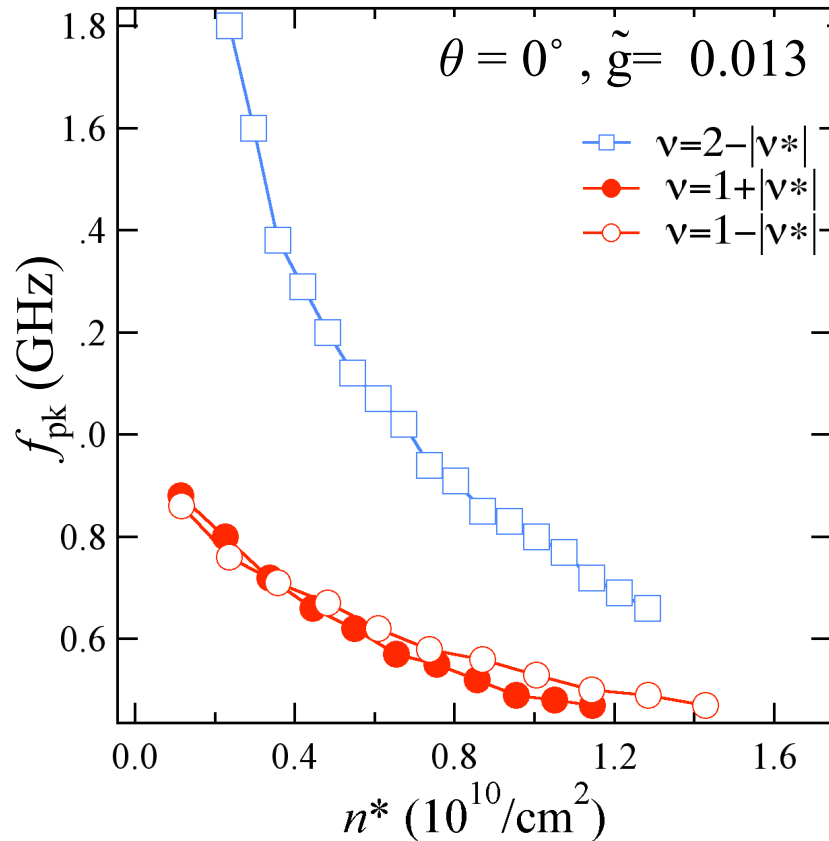
$$\theta = 63^\circ : \tilde{g} = 0.028$$

Same n^* , same Landau level index, $N=0$

Absence of any effect at $\nu=1.92$ indicates little effect of confinement due to B_{\parallel}

f_{pk} vs n^*

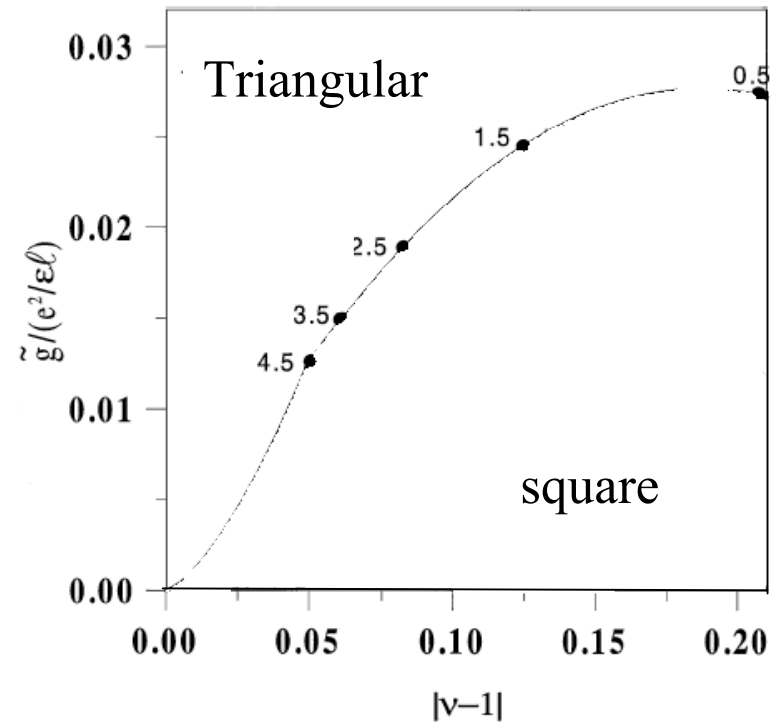
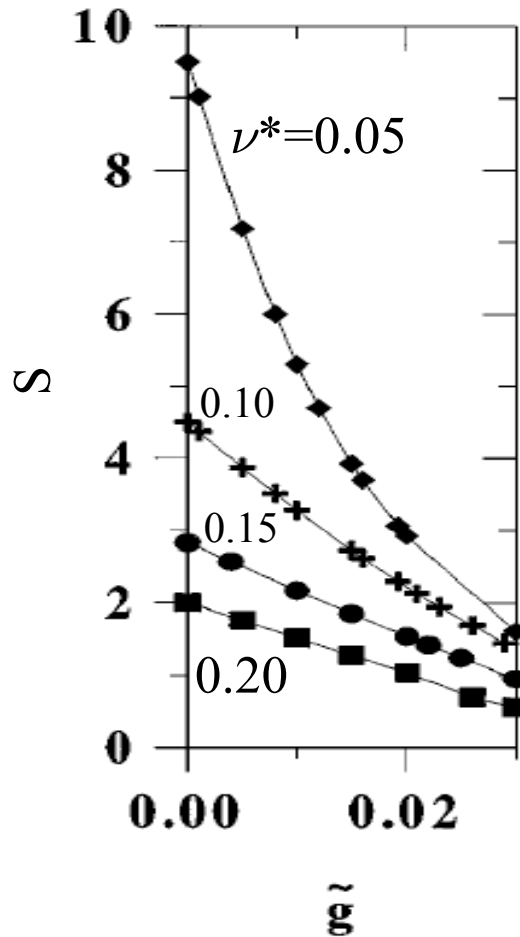
$n=1.15 \times 10^{11} \text{ cm}^{-2}$, $\mu \sim 10^7 \text{ cm}^2/\text{Vs}$
 $B=4.6 \text{ T}$ for $\nu=1$, $\theta=0^\circ$



Curves for $1 \pm \nu^*$ approach those for $2 - \nu^*$ as θ increases, so they lie together at largest n^*

Skyrmion crystals

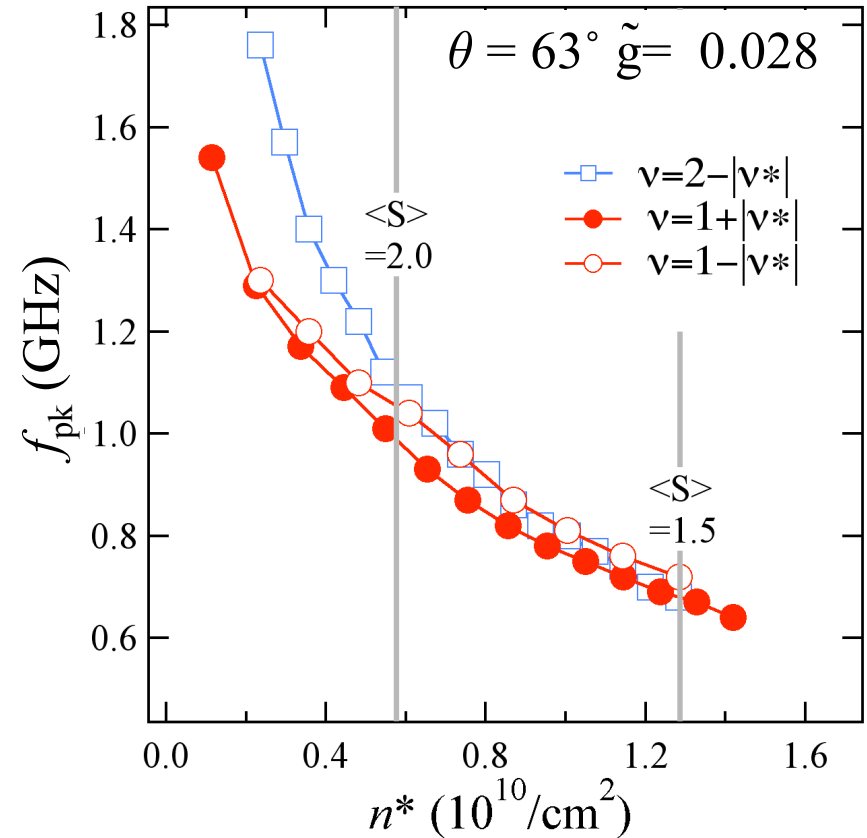
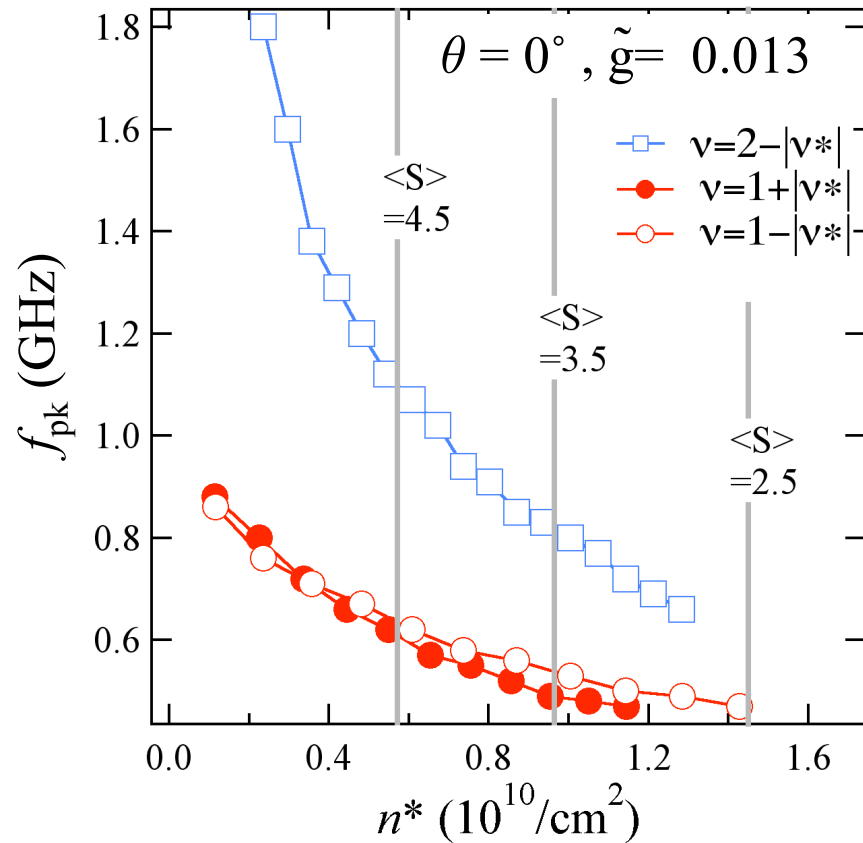
Côté, MacDonald, Brey, Fertig, Girvin, Stoof, PRL '97



- 1) Larger skyrmions are less favored when crystal is denser
- 2) Square to triangular transition

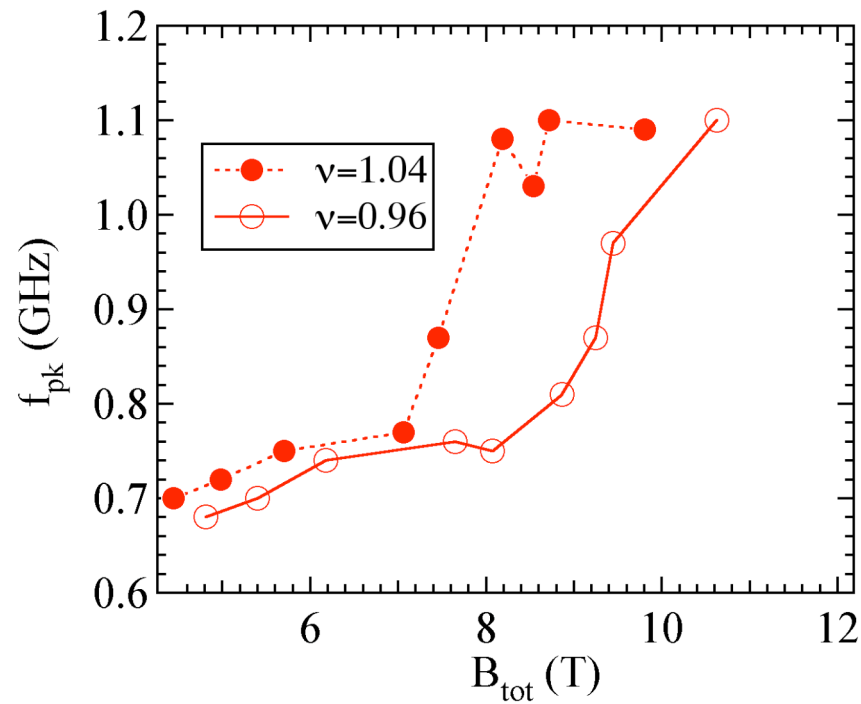
f_{pk} vs n^*

$n=1.15 \times 10^{11} \text{ cm}^{-2}$, $\mu \sim 10^7 \text{ cm}^2/\text{Vs}$
 $B=4.6 \text{ T}$ for $\nu=1$, $\theta=0^\circ$



f_{pk} difference visible for predicted $S > \sim 2$

Particle vs hole: different threshold B_{tot}



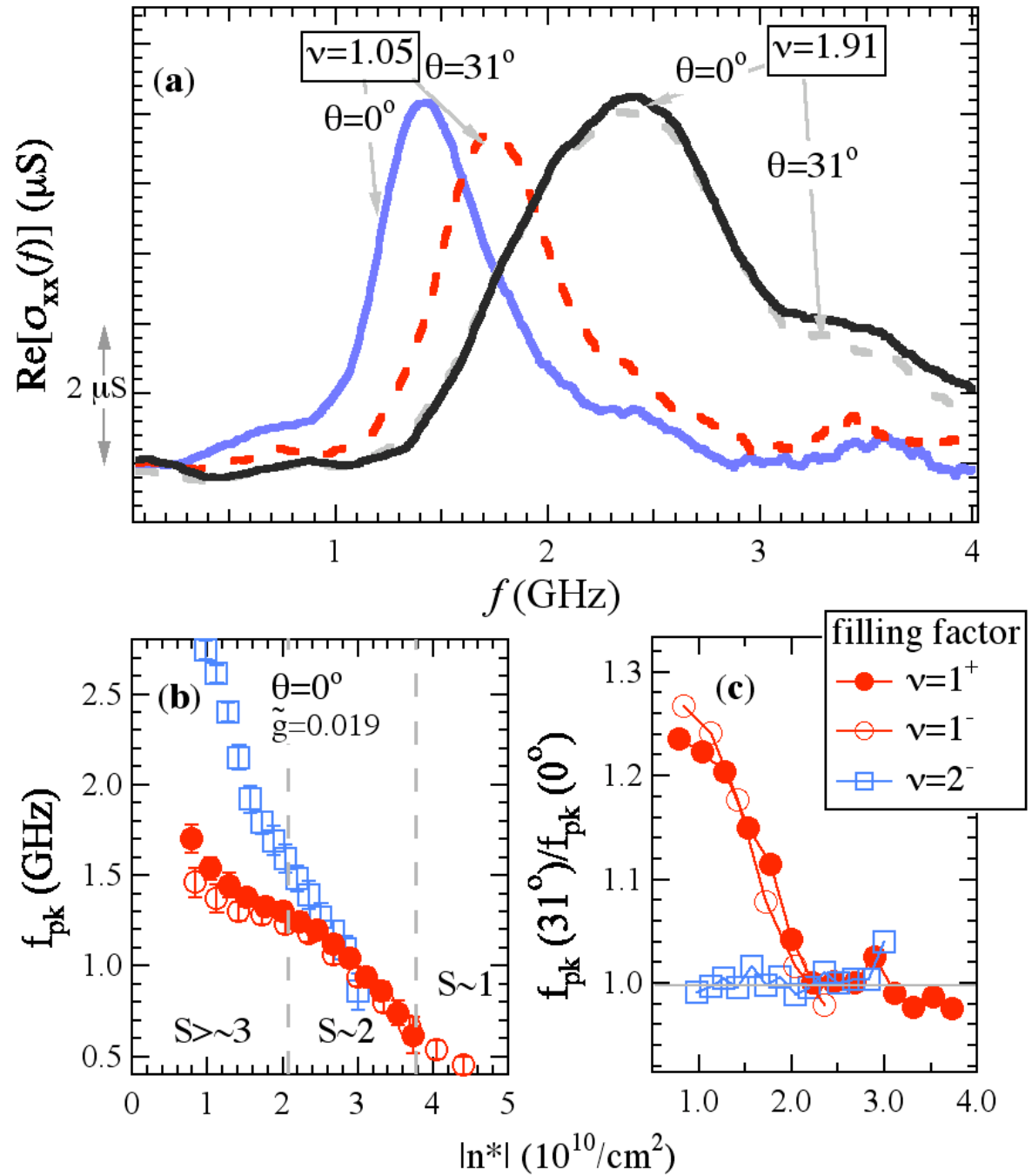
Different charge distribution in skyrmion vs antiskyrmion?

High n sample

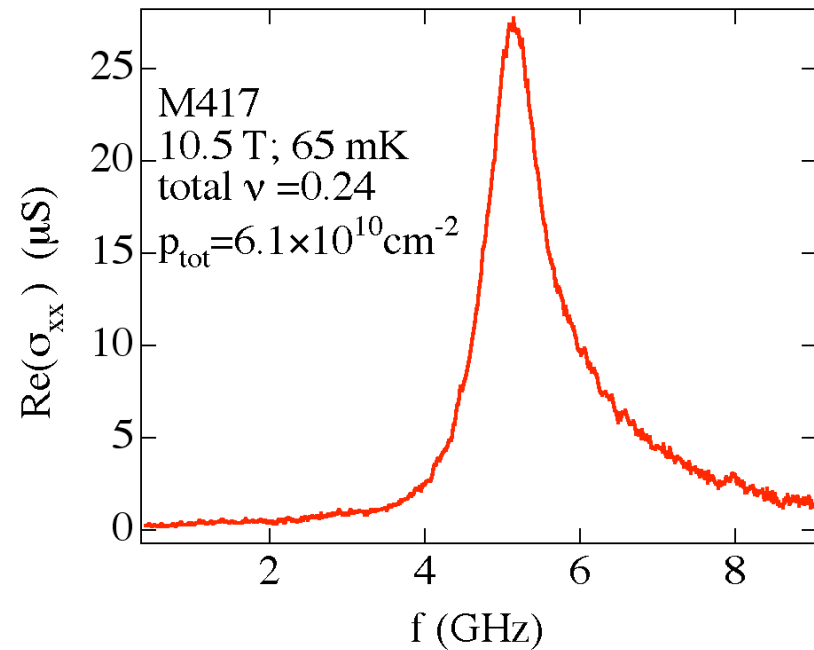
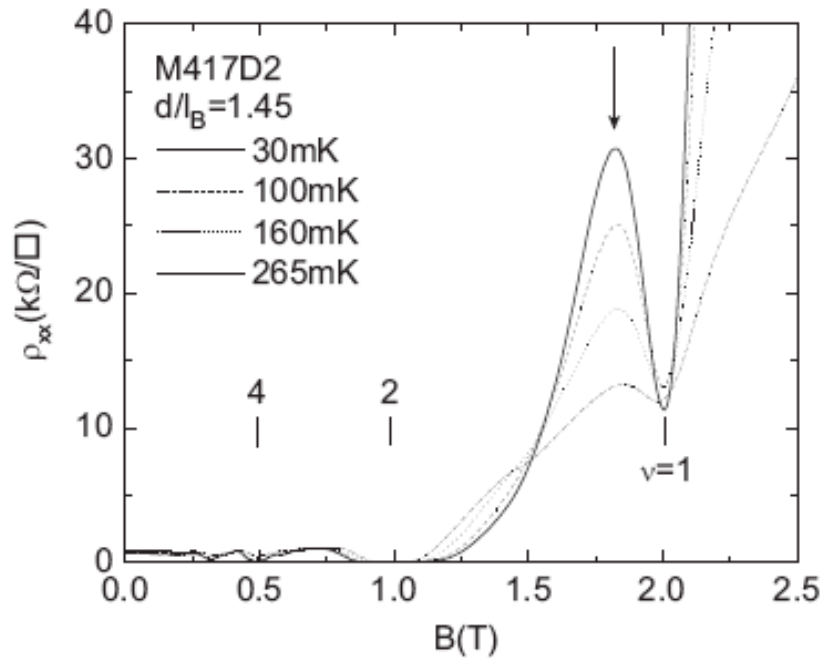
$n = 2.7 \times 10^{11} / \text{cm}^2$
 $\mu \sim 25 \times 10^6 \text{ cm}^2 / \text{Vs}$
 30 nm QW

Smaller range of θ

Larger \tilde{g} : 0.019 at 0°



High B Termination of QH series (bilayer)



Insulating phase accompanied by microwave resonance

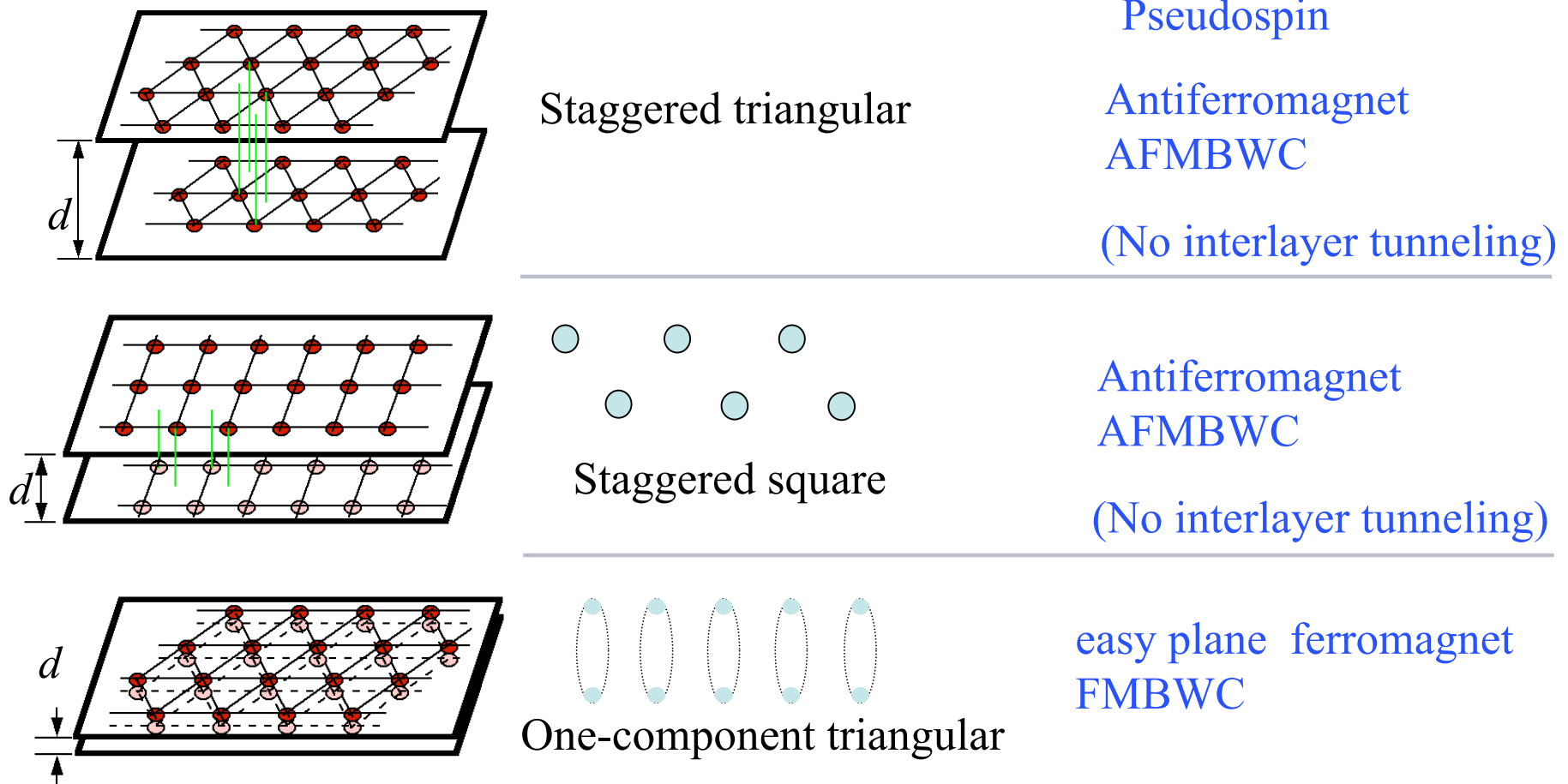
Bilayer p-type, per layer $p = 3.05 \times 10^{10} / \text{cm}^2$; well-center separation $d = 26 \text{ nm}$

$d / (\text{avg. spacing in a layer}) \sim d(\pi p)^{1/2} = 0.8$

(Earliest observation of pinning mode in bilayer: Doveston et al. 2002))

Bilayer Wigner Crystals (BWC) (balanced)

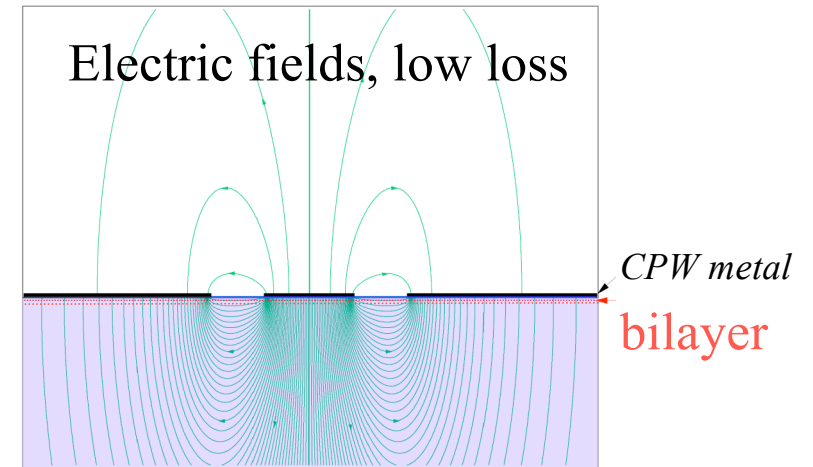
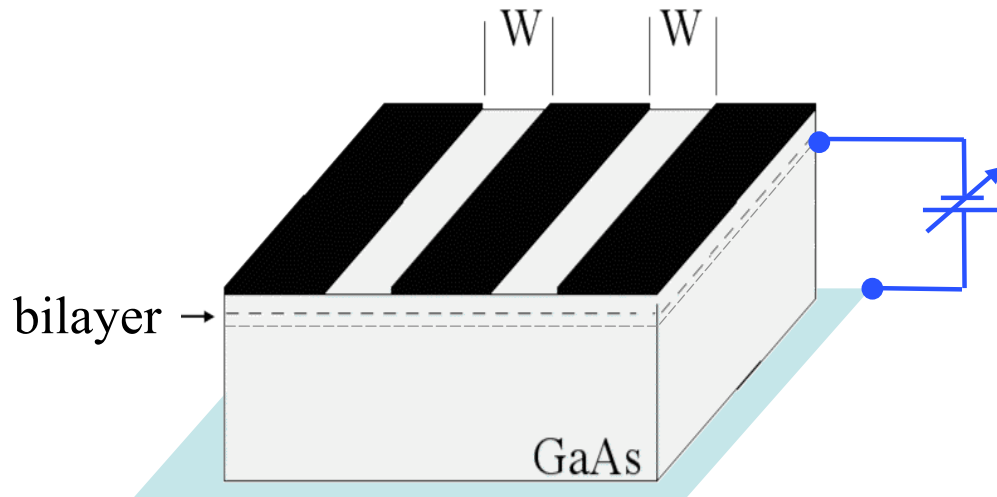
Type of BWC depends on **separation/ in-plane spacing**,
measured by $\tilde{d} = 2d(\pi p)^{1/2}$ p is density/layer (holes), d is well separation



Theories: Narasimhan and Ho, Zheng and Fertig. PRB '95

Evidence for phases: BWC pinning modes behavior $\Leftarrow \tilde{d}$

Microwave measurement, coupling to bilayer



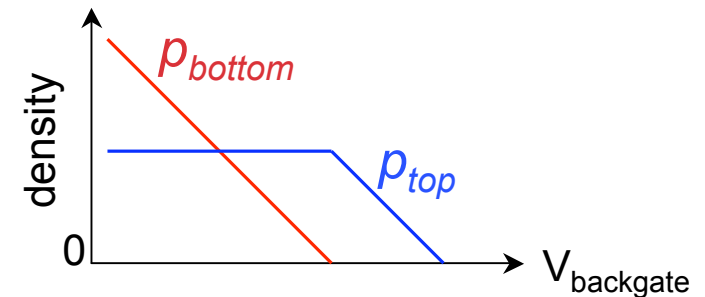
backgate only (no front gate)
one balanced density per cooldown

backgate only (no front gate) one
balanced density per cooldown

As cooled, $p_B > p_T$, + backgate bias decreases p_B first, p_T following p_B depletion

- Microwave electric field penetrates both layers with small perturbation

Independent layers with σ_1, σ_2 would give $(\sigma_1 + \sigma_2)$

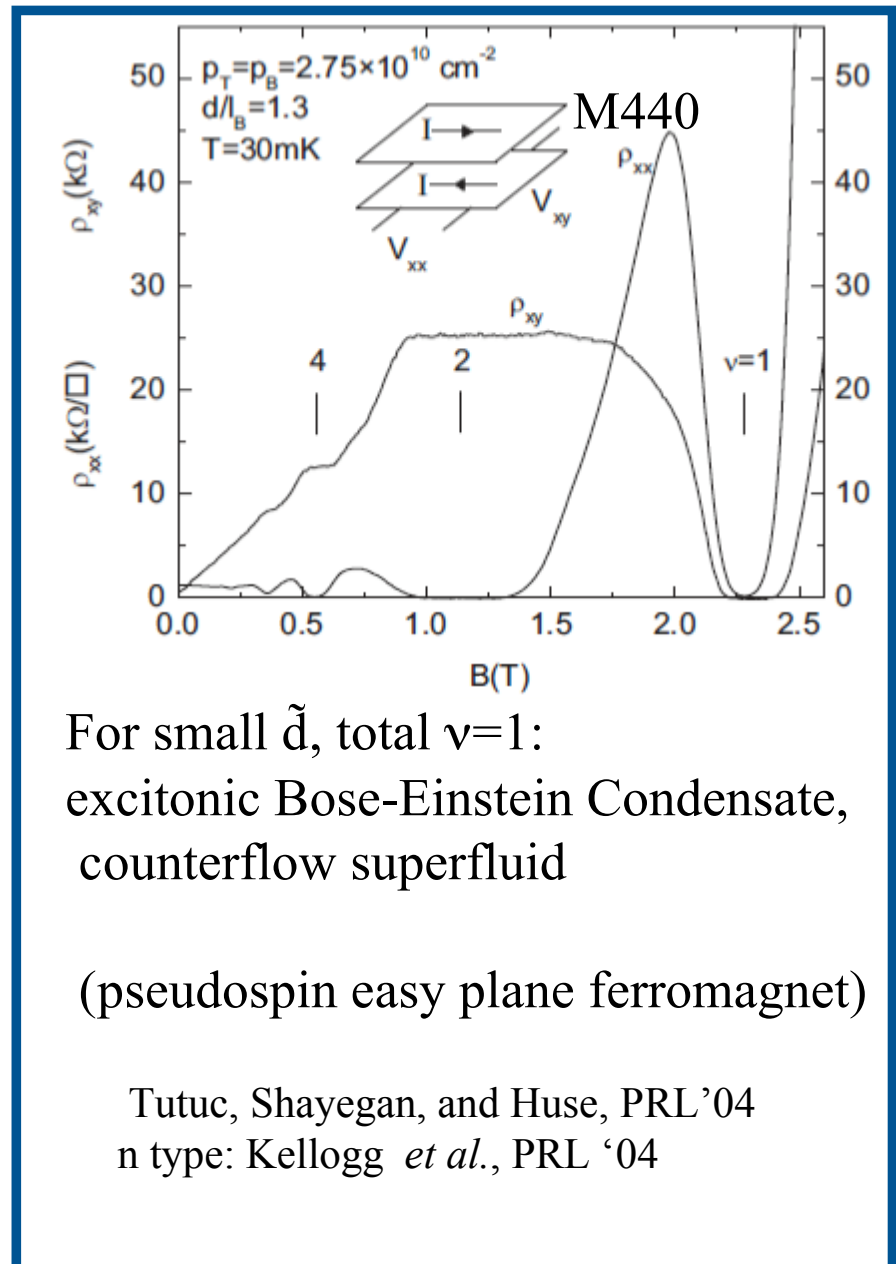


Samples

<311A> grown bilayers of holes
Negligible interlayer tunneling

Series of samples, $1.4 < \tilde{d} < 18$

deep in insulating phases, $\nu \approx 1/2$



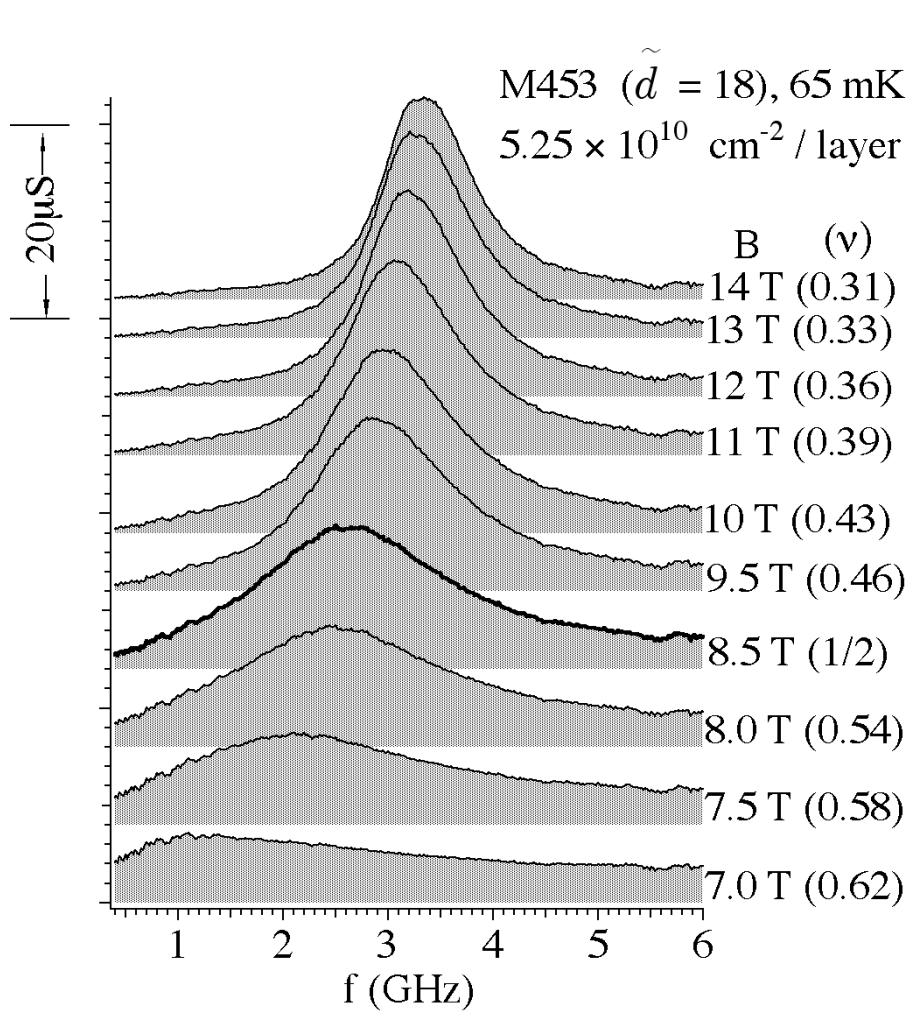
For small \tilde{d} , total $\nu=1$:
excitonic Bose-Einstein Condensate,
counterflow superfluid

(pseudospin easy plane ferromagnet)

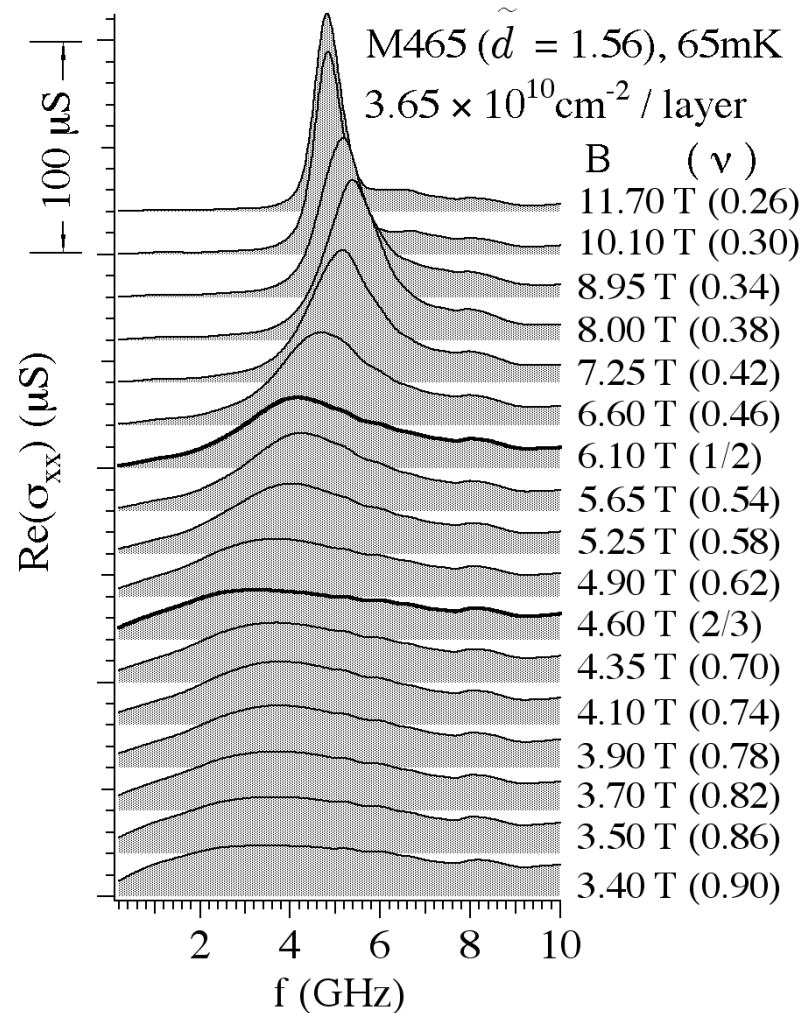
Tutuc, Shayegan, and Huse, PRL '04
n type: Kellogg *et al.*, PRL '04

($\tilde{d} = d/l_{BI}$, where l_{BI} is magnetic length when total filling $\nu = 1$)

Balanced BWC: Microwave Spectra, evolution with ν

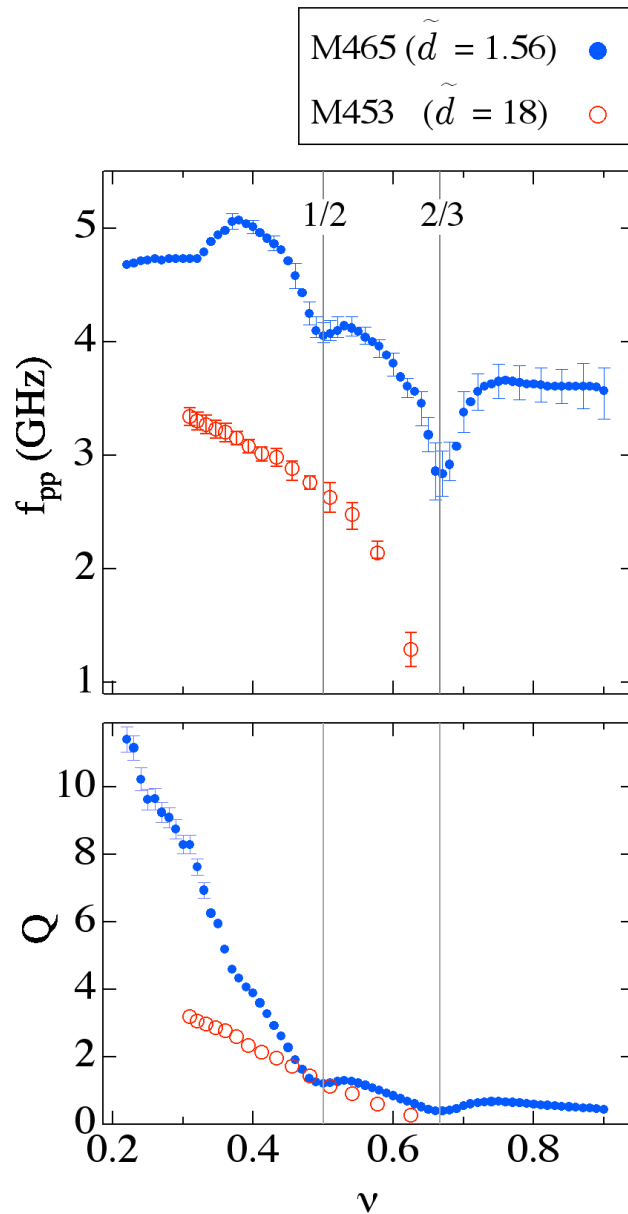


M453: Spectra similar to single-layer case.



M465: f_{pk} drop at $\nu=2/3$ & $1/2$, possibly indicating some FQH correlation in pinned bilayer WC.

Balanced BWC: Resonance f_{pk} and Q vs ν



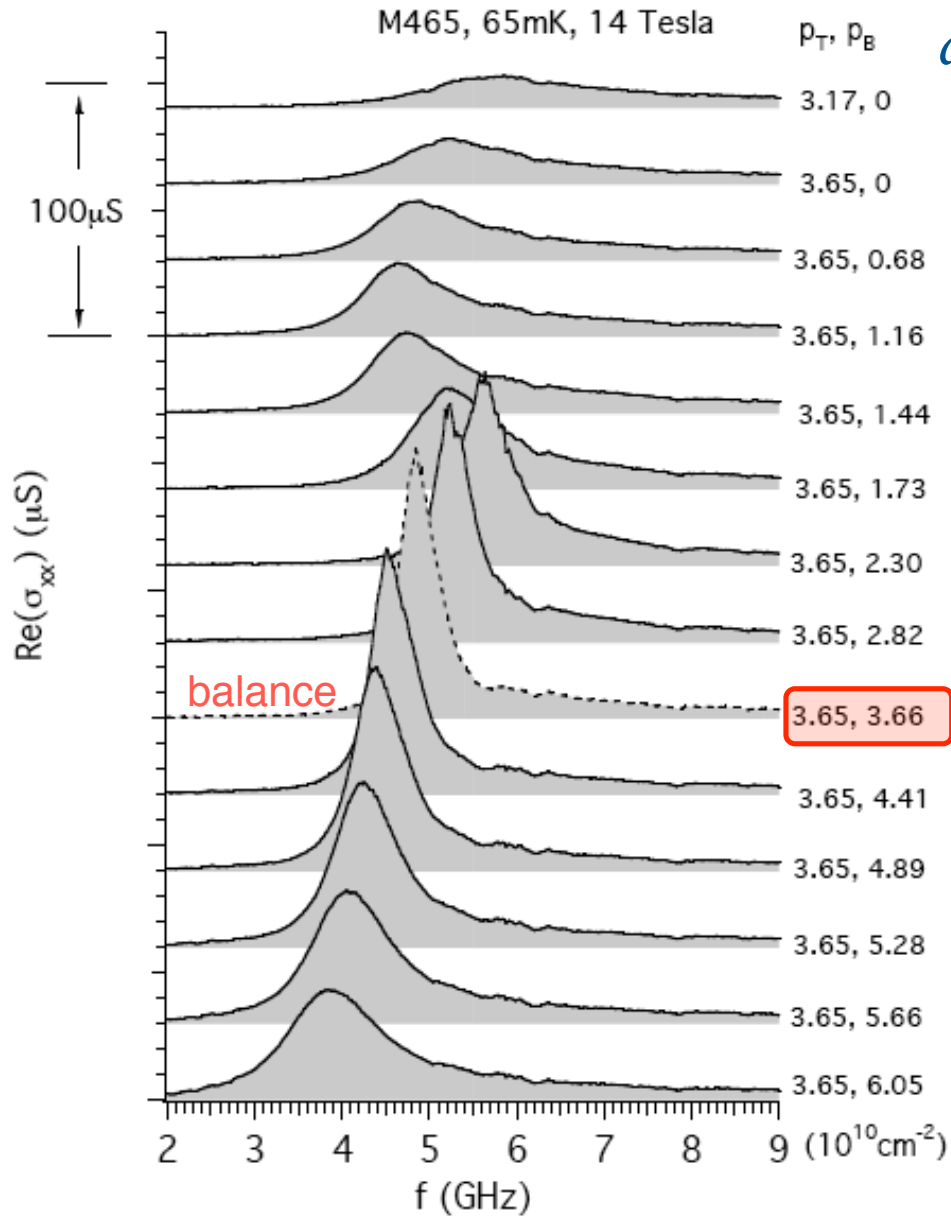
Dips in f_{pp} , Q at $\nu = 1/2, 2/3$

Clearly in insulating phase

FQH liquid correlations affect BWC
1/2: interlayer

In weak pinning: not softening of BWC
Reduction of pinning?

Imbalanced layer densities: Spectra at many p_{tot}



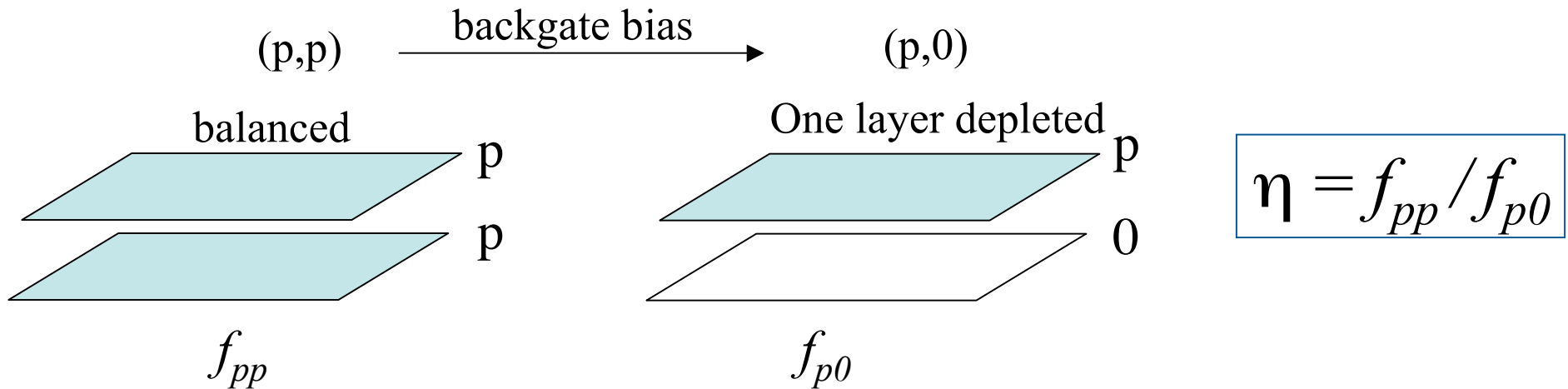
At imbalance,
significant density in each layer:

$\tilde{d} \leq 1.8$ One peak,

$\tilde{d} \geq 2.5$ Two peaks

V_{backgate}
increases

Series of samples, varying \tilde{d} : Single layer vs. Bi-layer

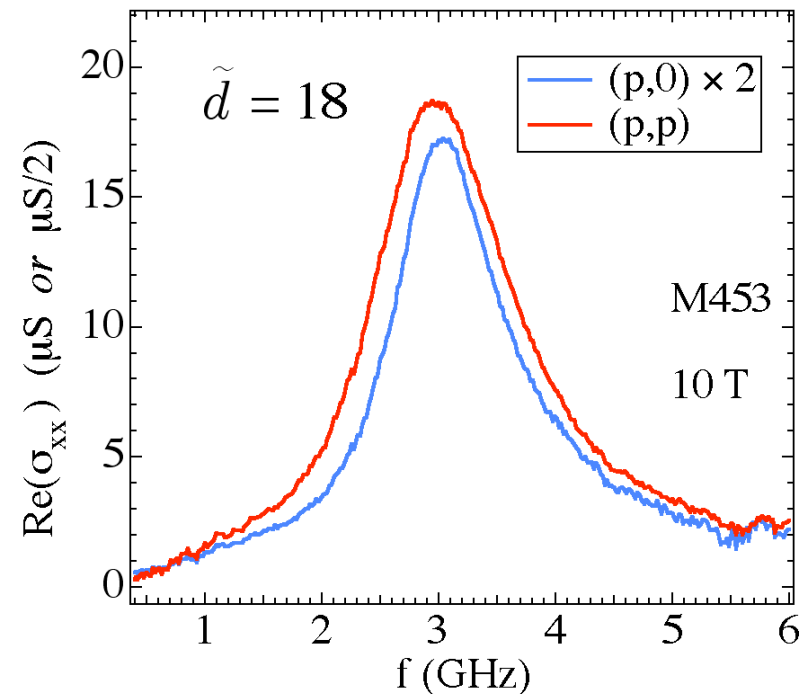


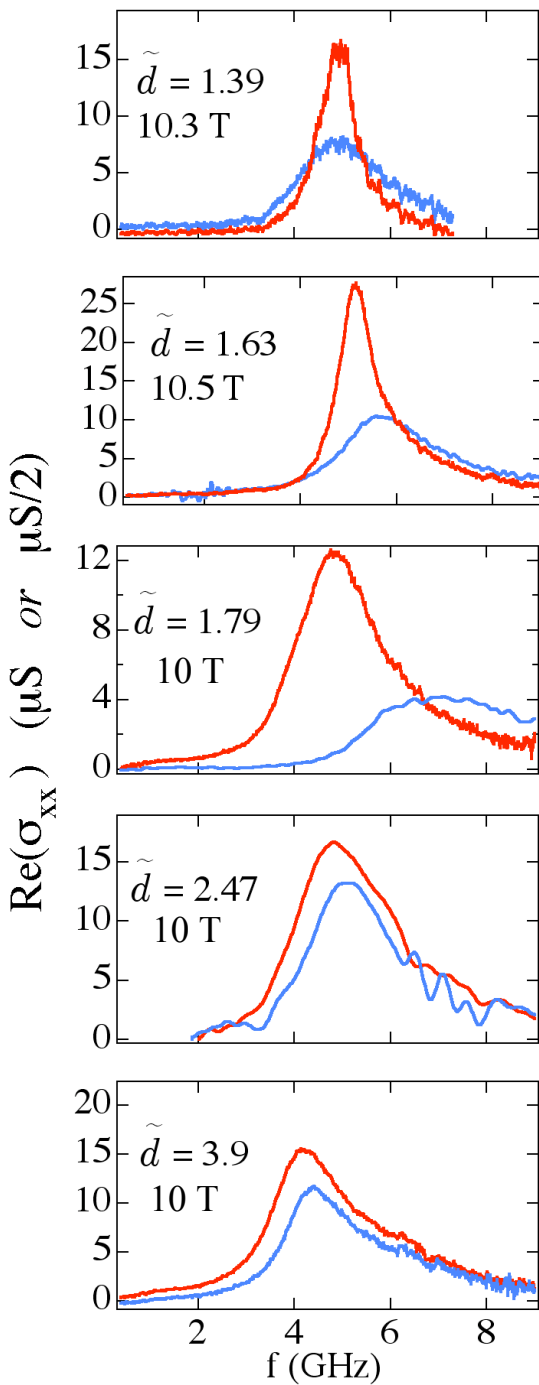
For independent layers \Rightarrow

$$\sigma_{xx;pp} = 2 \times \sigma_{xx;p0}$$

$$\eta = 1$$

Conductivity of (p,0) state is doubled on graph

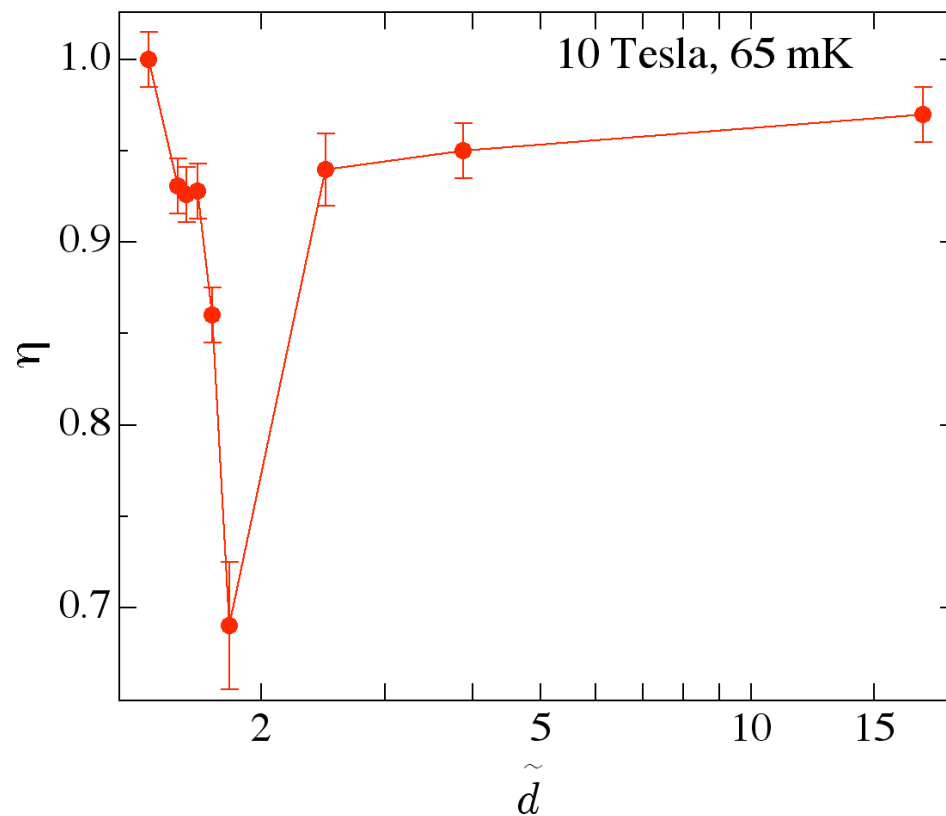




— (p,0) × 2
 — (p,p)

Series of samples, varying \tilde{d} :
 Single layer vs. Bi-layer

$$\eta = f_{pp} / f_{p0}$$



Density/ Carrier-carrier interaction

$$f_{pk} \propto (\text{density})^{-\gamma}$$

Weak pinning, classical

State: $(p,0) \rightarrow (p,p)$

$p_{\text{total}} : p \rightarrow 2p$

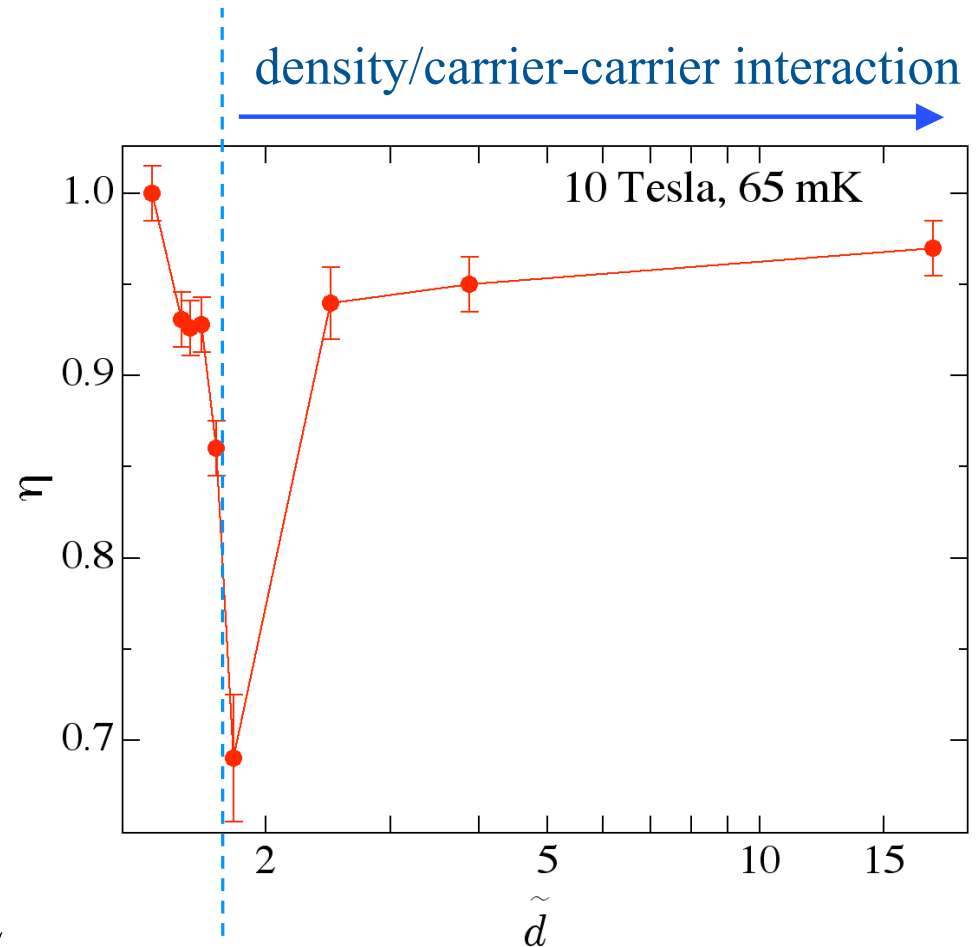
$$f_{p0} > f_{pp}$$

Small \tilde{d} limit : like one layer

maximal effect: $f \propto p_{\text{total}}^{-\gamma}$

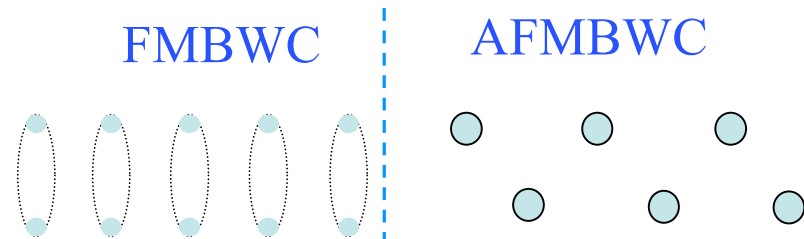
$$\eta = f_{pp}/f_{p0} \approx 0.71 \text{ for } \gamma=1/2$$

Larger $\tilde{d} \Rightarrow$ softer $(p,p) \Rightarrow$ larger η (closer to 1)



Question: how can η increase as \tilde{d} decreases?

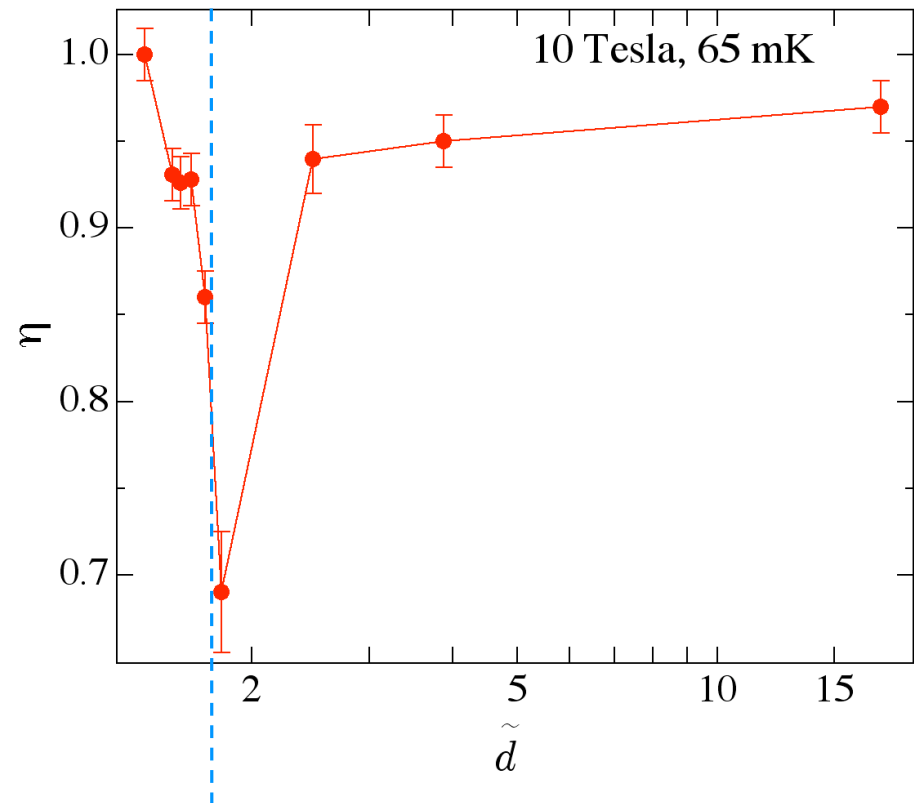
Interpretation: AFM \rightarrow FM BWC



- **FMBWC**: extra f_{pp} from disorder spatially correlated btw. wells (e.g. local tunneling at impurities)

Yong P. Chen, PRB **73**, 115314 (2006).

- Estimate transition at $\tilde{d}^* \sim 1.7$
- Exceeds theory predictions of $\tilde{d}^* \sim 0.4$ (Narasimhan and Ho, Zheng and Fertig '95)
- Comparison : $\nu=1$ excitonic Bose-Einstein condensate exists for $\tilde{d}^* < 1.8$.



“Applications” Summary

Skyrmions in IQHWC around $\nu = 1$

- Use rotation in field to vary E_Z , \tilde{g}
- n^* , \tilde{g} dependence of f_{pk} : consistent with $S \approx 2$ in Côté et al theory, gives reduced f_{pk}
- No sign of square to triangular transition

Bilayers

- Surveyed samples, negligible tunneling, for many \tilde{d}
- Compare (p,p) and (p,0) states to isolate effects of interlayer interaction
frequency ratio η shows striking minimum
- Interpretation:
 - $\tilde{d} > 1.7$: carrier-carrier interaction effect
 - $\tilde{d} < 1.7$: pinning enhanced in FMBWC